14-/12-Bit, 160/250MSPS, Ultralow-Power ADC

FEATURES

- **Maximum Sample Rate: 250MSPS**
- **Ultralow Power with 1.8V Single Supply:**
  - **200mW Total Power at 160MSPS**
  - **265mW Total Power at 250MSPS**
- **High Dynamic Performance:**
  - **SNR: 71.3dBFS at 170MHz**
  - **SFDR: 84dBc at 170MHz**
- **Dynamic Power Scaling with Sample Rate**
- **Output Interface**
  - **Double Data Rate (DDR) LVDS with Programmable Swing and Strength**
    - **Standard Swing: 350mV**
    - **Low Swing: 200mV**
    - **Default Strength: 100Ω Termination**
    - **2x Strength: 50Ω Termination**
  - **1.8V Parallel CMOS Interface Also Supported**
- **Programmable Gain up to 6dB for SNR/SFDR Trade-Off**
- **DC Offset Correction**
- **Supports Low Input Clock Amplitude Down To 400mV$_{PP}$**
- **Package: QFN-48 (7mm × 7mm)**

DESCRIPTION

The ADS414x/2x are a family of 14-bit/12-bit analog-to-digital converters (ADCs) with sampling rates up to 250MSPS. These devices use innovative design techniques to achieve high dynamic performance, while consuming extremely low power at 1.8V supply. The devices are well-suited for multi-carrier, wide bandwidth communications applications.

The ADS414x/2x have fine gain options that can be used to improve SFDR performance at lower full-scale input ranges, especially at high input frequencies. They include a dc offset correction loop that can be used to cancel the ADC offset. At lower sampling rates, the ADC automatically operates at scaled down power with no loss in performance.

The ADS414x/2x are available in a compact QFN-48 pacakge and are specified over the industrial temperature range (–40°C to +85°C).

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ADS412x/ADS414x Family Comparison

FAMILY	250MSPS	160MSPS	WITH ANALOG INPUT BUFFERS	
			250MSPS	200MSPS
ADS414x 14-Bit Family	ADS4149	ADS4146	ADS41B49	—
ADS412x 12-Bit Family	ADS4129	ADS4126	ADS41B29	—
11-Bit	—	—	—	ADS58B18

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

FUNCTIONAL BLOCK DIAGRAM

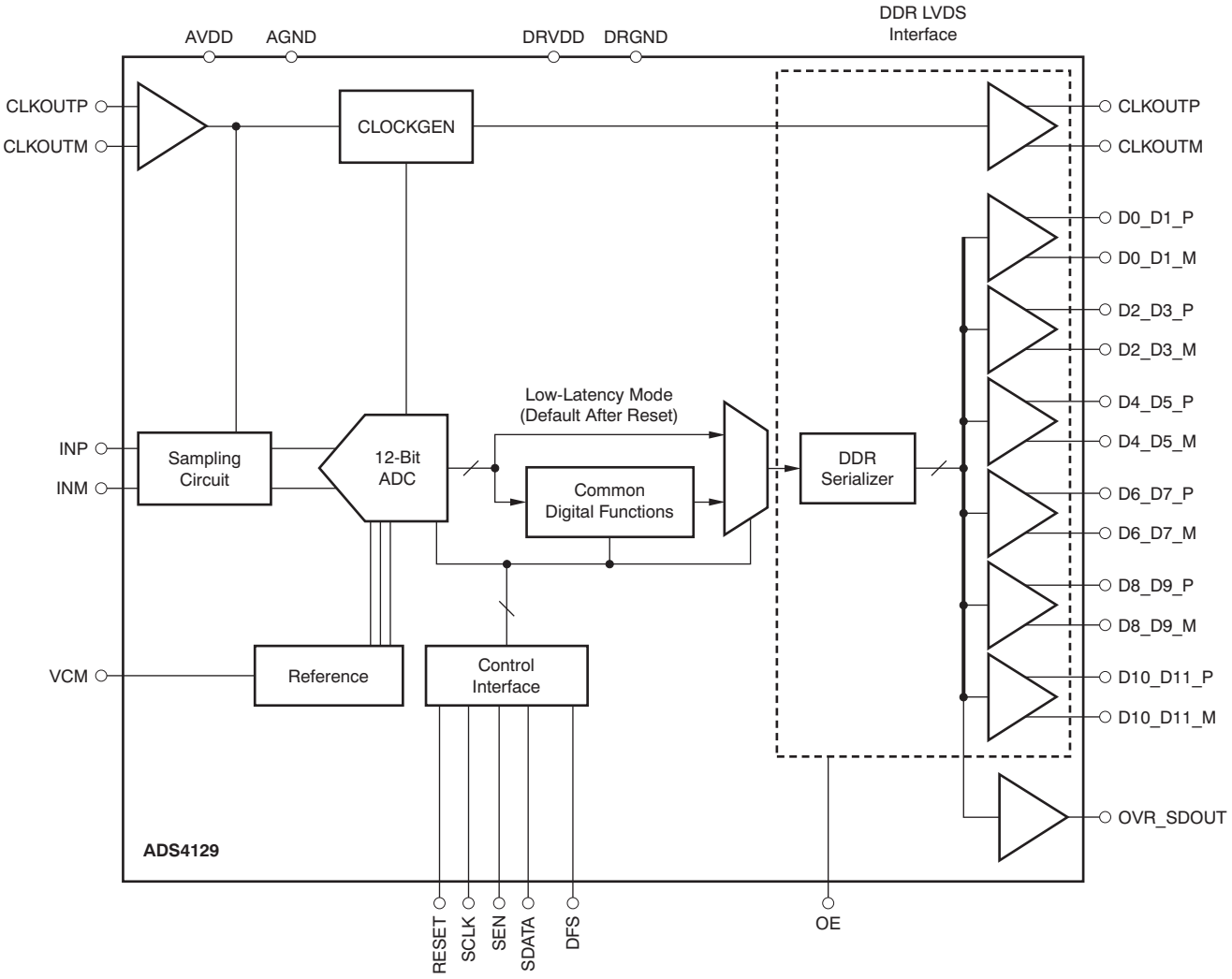

Figure 1. ADS412x Block Diagram

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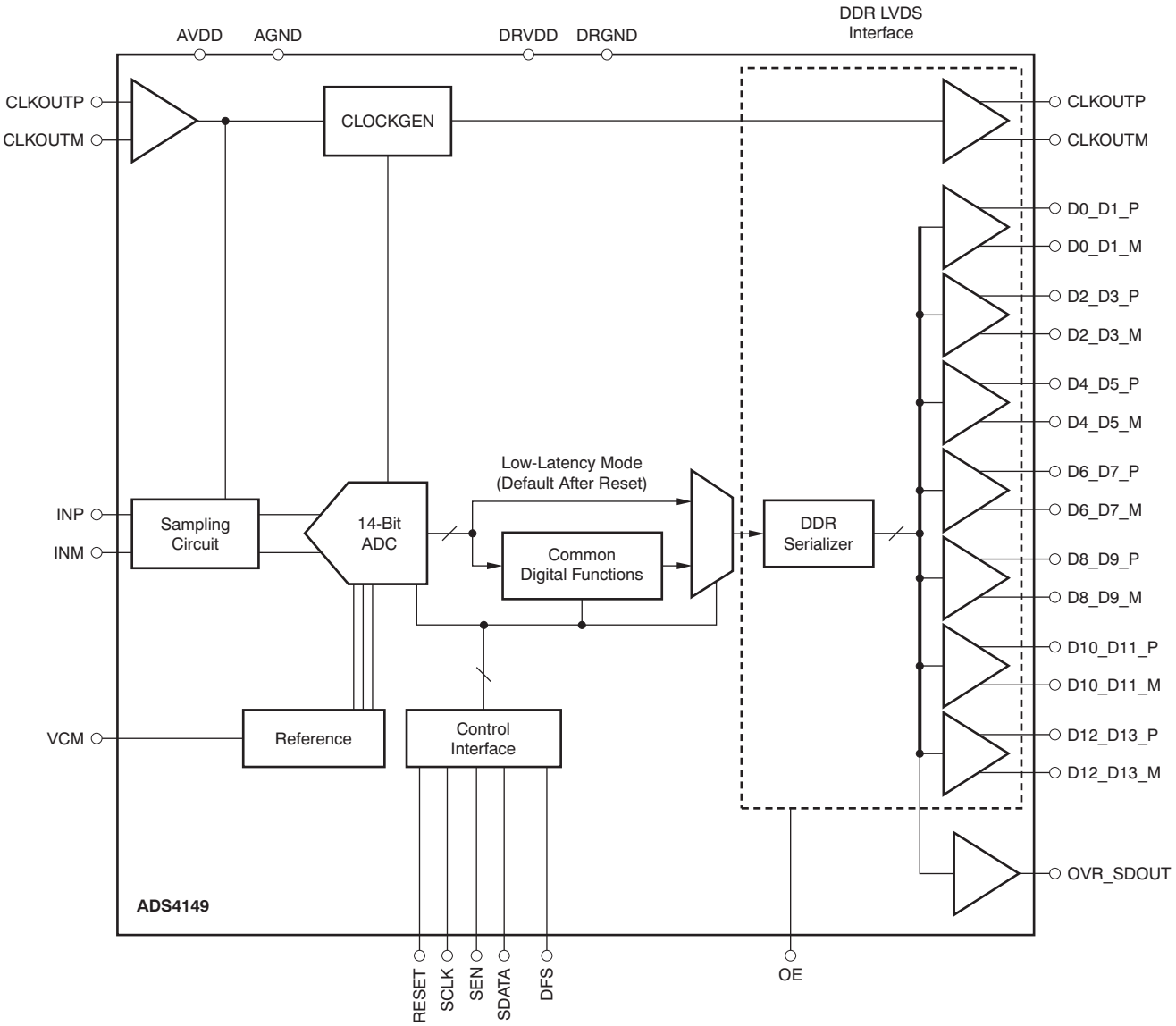

Figure 2. ADS414x Block Diagram

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ORDERING INFORMATION(1)

PRODUCT	PACKAGE-LEAD	PACKAGE DESIGNATOR	SPECIFIED TEMPERATURE RANGE	ECO PLAN(2)	LEAD/BALL FINISH	PACKAGE MARKING	ORDERING NUMBER	TRANSPORT MEDIA, QUANTITY
ADS4126	QFN-48	RGZ	–40°C to +85°C	GREEN (RoHS, no Sb/Br)	Cu/NiPdAu	AZ4126	ADS4126IRGZR	Tape and reel, TBD
							ADS4126IRGZT	Tape and reel, TBD
ADS4129	QFN-48	RGZ	–40°C to +85°C	GREEN (RoHS, no Sb/Br)	Cu/NiPdAu	AZ4129	ADS4129IRGZR	Tape and reel, TBD
							ADS4129IRGZT	Tape and reel, TBD
ADS4146	QFN-48	RGZ	–40°C to +85°C	GREEN (RoHS, no Sb/Br)	Cu/NiPdAu	AZ4146	ADS4146IRGZR	Tape and reel, TBD
							ADS4146IRGZT	Tape and reel, TBD
ADS4149	QFN-48	RGZ	–40°C to +85°C	GREEN (RoHS, no Sb/Br)	Cu/NiPdAu	AZ4149	ADS4149IRGZR	Tape and reel, TBD
							ADS4149IRGZT	Tape and reel, TBD

(1) For the most current package and ordering information see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
(2) Eco Plan is the planned eco-friendly classification. Green (RoHS, no Sb/Br): TI defines *Green* to mean Pb-Free (RoHS compatible) and free of Bromine- (Br) and Antimony- (Sb) based flame retardants. Refer to the Quality and Lead-Free (Pb-Free) Data web site for more information.

The ADS414x/2x family is almost pin compatable to the previous generation ADS6149 family; this enables easy migration. However, there are some important differences that are listed in Table 1.

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Table 1. MIGRATING FROM THE ADS6149 FAMILY

ADS6149 FAMILY	ADS4149 FAMILY
PINS	
Pin 21 is NC (not connected)	Pin 21 is NC (not connected)
Pin 23 is MODE	Pin 23 is a digital control pin for the RESERVED function.
SUPPLY	
AVDD is 3.3V	AVDD is 1.8V
DRVDD is 1.8V	No change
INPUT COMMON-MODE VOLTAGE	
VCM is 1.5V	VCM is 0.95V
SERIAL INTERFACE	
Protocol: 8-bit register address and 8-bit register data	No change in protocol
	New serial register map
EXTERNAL REFERENCE MODE	
Supported	Not supported
ADS61B49 FAMILY	**ADS41B29/B49/ADS58B18 FAMILY**
PINS	
Pin 21 is NC (not connected)	Pin 21 is 3.3V AVDD_BUF (supply for the analog input buffers)
Pin 23 is MODE	Pin 23 is a digital control pin for the RESERVED function. Pin 23 functions as SNR Boost enable (B18 only).
SUPPLY	
AVDD is 3.3V	AVDD is 1.8V, AVDD_BUF is 3.3V
DRVDD is 1.8V	No change
INPUT COMMON-MODE VOLTAGE	
VCM is 1.5V	VCM is 0.95V
SERIAL INTERFACE	
Protocol: 8-bit register address and 8-bit register data	No change in protocol New serial register map
EXTERNAL REFERENCE MODE	
Supported	Not supported

ABSOLUTE MAXIMUM RATINGS(1)

Over operating free-air temperature range, unless otherwise noted.

		VALUE	UNIT
Supply voltage range, AVDD		–0.3 to 2.1	V
Supply voltage range, DRVDD		–0.3 to 2.1	V
Voltage between AGND and DRGND		–0.3 to 0.3	V
Voltage between AVDD to DRVDD (when AVDD leads DRVDD)		0 to 2.1	V
Voltage between DRVDD to AVDD (when DRVDD leads AVDD)		0 to 2.1	V
Voltage applied to input pins	INP, INM	–0.3 to minimum (1.9, AVDD + 0.3)	V
	CLKP, CLKM(2), DFS, OE	–0.3 to AVDD + 0.3	V
	RESET, SCLK, SDATA, SEN	–0.3 to 3.9	V
Operating free-air temperature range, T_A		–40 to +85	°C
Operating junction temperature range, T_J		+125	°C
Storage temperature range, T_{STG}		–65 to +150	°C
ESD, human body model (HBM)		TBD	kV

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
(2) When AVDD is turned off, it is recommended to switch off the input clock (or ensure the voltage on CLKP, CLKM is less than |0.3V|. This prevents the ESD protection diodes at the clock input pins from turning on.

THERMAL CHARACTERISTICS(1)

PARAMETER	TEST CONDITIONS	TYPICAL VALUE	UNIT
$R_{\theta JA}$ (2)	Soldered thermal pad, no airflow	29	°C/W
	Soldered thermal pad, 200LFM	22	°C/W
$R_{\theta JT}$ (3)	Bottom of package (thermal pad)	1.13	°C/W

(1) With a JEDEC standard high-K board and 5×5 via array. See the *Exposed Pad* section in the *Application Information* .
(2) $R_{\theta JA}$ is the thermal resistance from junction to ambient.
(3) $R_{\theta JT}$ is the thermal resistance from junction to the thermal pads.

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RECOMMENDED OPERATING CONDITIONS

Over operating free-air temperature range, unless otherwise noted.

		ADS412x, ADS414x			UNIT
		MIN	TYP	MAX	
SUPPLIES					
AVDD	Analog supply voltage	TBD	1.8	TBD	V
DRVDD	Digital supply voltage	TBD	1.8	TBD	V
ANALOG INPUTS					
Differential input voltage range(1)			2		V_{PP}
Input common-mode voltage			V_{CM} ± 0.1		V
Maximum analog input frequency with $2V_{PP}$ input amplitude(2)			TBD		MHz
Maximum analog input frequency with $1V_{PP}$ input amplitude(2)			TBD		MHz
CLOCK INPUT					
Input clock sample rate					
ADS4129/ADS4149		1		250	MSPS
ADS4126/ADS4146		1		160	MSPS
Input clock amplitude differential ($V_{CLKP} – V_{CLKM}$)					
	Sine wave, ac-coupled	TBD	1.5		V_{PP}
	LVPECL, ac-coupled		1.6		V_{PP}
	LVDS, ac-coupled		0.7		V_{PP}
	LVCMOS, single-ended, ac-coupled		1.8		V
Input clock duty cycle			50		%
DIGITAL OUTPUTS					
C_{LOAD}	Maximum external load capacitance from each output pin to DRGND		5		pF
R_{LOAD}	Differential load resistance between the LVDS output pairs (LVDS mode)		100		Ω
T_A	Operating free-air temperature	–40		+85	°C

(1) With 0dB gain. See the **Gain Programmability** section in the *Application Information* for relation between input voltage range and gain.
(2) See the *Theory of Operation* section in the *Application Information* .

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ELECTRICAL CHARACTERISTICS: ADS4146/ADS4149

Typical values are at +25°C, AVDD = 1.8V, DRVDD = 1.8V, 50% clock duty cycle, and –1dBFS differential analog input, unless otherwise noted. Minimum and maximum values are across the full temperature range: T_{MIN} = –40°C to T_{MAX} = +85°C, AVDD = 1.8V, and DRVDD = 1.8V.

PARAMETER	TEST CONDITIONS	ADS4146 (160MSPS)			ADS4149 (250MSPS)			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
Resolution				14			14	Bits
SNR (signal-to-noise ratio), LVDS	f_{IN} = 10MHz		73.7			73		dBFS
	f_{IN} = 70MHz		73.2			72.5		dBFS
	f_{IN} = 100MHz		72.8			72.2		dBFS
	f_{IN} = 170MHz		71.5			71.2		dBFS
	f_{IN} = 300MHz		69.8			69.8		dBFS
SINAD (signal-to-noise and distortion ratio), LVDS	f_{IN} = 10MHz		73.3			72.8		dBFS
	f_{IN} = 70MHz		72.9			72.1		dBFS
	f_{IN} = 100MHz		72.6			71.7		dBFS
	f_{IN} = 170MHz		71.1			70.9		dBFS
	f_{IN} = 300MHz		68.6			67.8		dBFS
Spurious-free dynamic range SFDR	f_{IN} = 10MHz		85			88		dBc
	f_{IN} = 70MHz		87			84		dBc
	f_{IN} = 100MHz		86			82		dBc
	f_{IN} = 170MHz		83.5			85		dBc
	f_{IN} = 300MHz		76.5			73		dBc
Total harmonic distortion THD	f_{IN} = 10MHz		83.5			85		dBc
	f_{IN} = 70MHz		84.7			82		dBc
	f_{IN} = 100MHz		83.8			80		dBc
	f_{IN} = 170MHz		81.2			82.5		dBc
	f_{IN} = 300MHz		74			71		dBc
Second-harmonic distortion HD2	f_{IN} = 10MHz		85			88		dBc
	f_{IN} = 70MHz		88			86		dBc
	f_{IN} = 100MHz		87			86		dBc
	f_{IN} = 170MHz		87			85		dBc
	f_{IN} = 300MHz		77.5			73		dBc
Third-harmonic distortion HD3	f_{IN} = 10MHz		90			89		dBc
	f_{IN} = 70MHz		88			84		dBc
	f_{IN} = 100MHz		87			82		dBc
	f_{IN} = 170MHz		83.5			88		dBc
	f_{IN} = 300MHz		76.5			78		dBc
Worst spur (other than second and third harmonics)	f_{IN} = 10MHz		95			92		dBc
	f_{IN} = 70MHz		95			90		dBc
	f_{IN} = 100MHz		93			91		dBc
	f_{IN} = 170MHz		92			92		dBc
	f_{IN} = 300MHz		88			87		dBc
Two-tone intermodulation distortion IMD	f_1 = 46MHz, f_2 = 50MHz, each tone at –7dBFS		TBD			TBD		dBFS
	f_1 = 185MHz, f_2 = 190MHz, each tone at –7dBFS		TBD			TBD		dBFS
Input overload recovery	Recovery to within 1% (of final value) for 6dB overload with sine-wave input		1			1		Clock cycles
AC power-supply rejection ratio PSRR	For 100mV_{PP} signal on AVDD supply, up to 10MHz		> 30			> 30		dB
Effective number of bits ENOB	f_{IN} = 170MHz		11.5			TBD		LSBs
Differential nonlinearity DNL	f_{IN} = TBDMHz		TBD			TBD		LSBs
Integrated nonlinearity INL	f_{IN} = TBDMHz		TBD			TBD		LSBs

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ELECTRICAL CHARACTERISTICS: ADS4126/ADS4129

Typical values are at +25°C, AVDD = 1.8V, DRVDD = 1.8V, 50% clock duty cycle, and –1dBFS differential analog input, unless otherwise noted. Minimum and maximum values are across the full temperature range: T_{MIN} = –40°C to T_{MAX} = +85°C, AVDD = 1.8V, and DRVDD = 1.8V.

PARAMETER	TEST CONDITIONS	ADS4126 (160MSPS)			ADS4129 (250MSPS)			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
Resolution				12			12	Bits
SNR (signal-to-noise ratio), LVDS	f_{IN} = 10MHz		71			70.6		dBFS
	f_{IN} = 70MHz		70.7			70.3		dBFS
	f_{IN} = 100MHz		70.5			70.2		dBFS
	f_{IN} = 170MHz		69.6			69.5		dBFS
	f_{IN} = 300MHz		68.5			68.5		dBFS
SINAD (signal-to-noise and distortion ratio), LVDS	f_{IN} = 10MHz		70.8			70.5		dBFS
	f_{IN} = 70MHz		70.5			70		dBFS
	f_{IN} = 100MHz		70.3			69.8		dBFS
	f_{IN} = 170MHz		69.4			69.3		dBFS
	f_{IN} = 300MHz		67.5			66.9		dBFS
Spurious-free dynamic range SFDR	f_{IN} = 10MHz		85			88		dBc
	f_{IN} = 70MHz		87			83		dBc
	f_{IN} = 100MHz		88			82		dBc
	f_{IN} = 170MHz		83			84.5		dBc
	f_{IN} = 300MHz		76			72.5		dBc
Total harmonic distortion THD	f_{IN} = 10MHz		83.5			85		dBc
	f_{IN} = 70MHz		84.7			81		dBc
	f_{IN} = 100MHz		83.8			80		dBc
	f_{IN} = 170MHz		81.2			82		dBc
	f_{IN} = 300MHz		74			71		dBc
Second-harmonic distortion HD2	f_{IN} = 10MHz		85			90		dBc
	f_{IN} = 70MHz		89			87		dBc
	f_{IN} = 100MHz		87			86		dBc
	f_{IN} = 170MHz		87			84.5		dBc
	f_{IN} = 300MHz		77			72.5		dBc
Third-harmonic distortion HD3	f_{IN} = 10MHz		90			88		dBc
	f_{IN} = 70MHz		87			83		dBc
	f_{IN} = 100MHz		87			82		dBc
	f_{IN} = 170MHz		83			87		dBc
	f_{IN} = 300MHz		76			78		dBc
Worst spur (other than second and third harmonics)	f_{IN} = 10MHz		94			92		dBc
	f_{IN} = 70MHz		94			90		dBc
	f_{IN} = 100MHz		92			91		dBc
	f_{IN} = 170MHz		91			92		dBc
	f_{IN} = 300MHz		88			87		dBc
Two-tone intermodulation distortion IMD	f_1 = 46MHz, f_2 = 50MHz, each tone at –7dBFS		TBD			TBD		dBFS
	f_1 = 185MHz, f_2 = 190MHz, each tone at –7dBFS		TBD			TBD		dBFS
Input overload recovery	Recovery to within 1% (of final value) for 6dB overload with sine-wave input		1			1		Clock cycles
AC power-supply rejection ratio PSRR	For 100mV_{PP} signal on AVDD supply, up to 10MHz		> 30			> 30		dB
Effective number of bits ENOB	f_{IN} = 170MHz		11.2			11.2		LSBs
Differential nonlinearity DNL			TBD			TBD		LSBs
Integrated nonlinearity INL			TBD			TBD		LSBs

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ELECTRICAL CHARACTERISTICS: GENERAL

Typical values are at +25°C, AVDD = 1.8V, DRVDD = 1.8V, 50% clock duty cycle, and –1dBFS differential analog input, unless otherwise noted. Minimum and maximum values are across the full temperature range: T_{MIN} = –40°C to T_{MAX} = +85°C, AVDD = 1.8V, and DRVDD = 1.8V.

PARAMETER	ADS4126/ADS4146 (160MSPS)			ADS4129/ADS4149 (250MSPS)			UNIT
	MIN	TYP	MAX	MIN	TYP	MAX	
ANALOG INPUTS							
Differential input voltage range		2.0			2.0		V_{PP}
Differential input resistance (at dc); see Figure 118		> 1			> 1		MΩ
Differential input capacitance; see Figure 119		4			4		pF
Analog input bandwidth		550			550		MHz
Analog input common-mode current (per input pin)		1.2			1.2		µA/MSPS
Common-mode output voltage VCM		0.95			0.95		V
VCM output current capability		TBD			TBD		mA
DC ACCURACY							
Offset error		2.5			2.5		mV
Temperature coefficient of offset error		TBD			TBD		mV/°C
Variation of offset error with supply		TBD			TBD		mV/V
Gain error as a result of internal reference inaccuracy alone E_{GREF}		TBD			TBD		%FS
Gain error of channel alone E_{GCHAN}		TBD			TBD		%FS
Temperature coefficient of E_{GCHAN}		TBD			TBD		Δ%/°C
POWER SUPPLY							
IAVDD Analog supply current		73			99		mA
IDRVDD(1) Output buffer supply current LVDS interface with 100Ω external termination Low LVDS swing (200mV)		38			47		mA
IDRVDD Output buffer supply current LVDS interface with 100Ω external termination Standard LVDS swing (350mV)		50			59		mA
IDRVDD output buffer supply current(1) (2) CMOS interface(2) 10pF external load capacitance f_{IN} = 3MHz		TBD			TBD		
Analog power		131			179		mW
Digital power		68.7			84.6		mW
LVDS interface, low LVDS swing Digital power CMOS interface(2) 10pF external load capacitance f_{IN} = 3MHz		TBD			TBD		mW
Global power-down		5			5		mW
Standby		TBD			TBD		mW

(1) The maximum DRVDD current with CMOS interface depends on the actual load capacitance on the digital output lines. Note that the maximum recommended load capacitance on each digital output line is 10pF.

(2) In CMOS mode, the DRVDD current scales with the sampling frequency, the load capacitance on output pins, input frequency, and the supply voltage (see the *CMOS Interface Power Dissipation* section in the *Application Information*).

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DIGITAL CHARACTERISTICS

Typical values are at +25°C, AVDD = 1.8V, DRVDD = 1.8V, 50% clock duty cycle, and –1dBFS differential analog input, unless otherwise noted. Minimum and maximum values are across the full temperature range: T_{MIN} = –40°C to T_{MAX} = +85°C, AVDD = 1.8V, and DRVDD = 1.8V.

PARAMETER	TEST CONDITIONS	ADS4126, ADS4129, ADS4146, ADS4149			UNIT
		MIN	TYP	MAX	
DIGITAL INPUTS (RESET, SCLK, SDATA, SEN, OE)					
High-level input voltage	RESET, SCLK, SDATA, and SEN support 1.8V and 3.3V CMOS logic levels	TBD	> 1.3		V
Low-level input voltage			< 0.4	TBD	V
High-level input voltage	OE only supports 1.8V CMOS logic levels		> 1.3		V
Low-level input voltage			< 0.4		V
High-level input current: SDATA, SCLK(1)	V_{HIGH} = 1.8V		TBD		µA
High-level input current: SEN	V_{HIGH} = 1.8V		TBD		µA
Low-level input current: SDATA, SCLK	V_{LOW} = 0V		TBD		µA
Low-level input current: SEN	V_{LOW} = 0V		TBD		µA
Input capacitance			TBD		pF
DIGITAL OUTPUTS (CMOS INTERFACE: D0 TO D13, OVR_SDOUT)					
High-level output voltage		TBD	DRVDD		V
Low-level output voltage			0	TBD	V
DIGITAL OUTPUTS (LVDS INTERFACE: DA0P/M TO DA13P/M, DB0P/M TO DB13P/M, CLKOUTP/M)					
High-level output voltage(2) V_{ODH}	Standard swing LVDS	TBD	+350	TBD	mV
Low-level output voltage(2) V_{ODL}	Standard swing LVDS	TBD	–350	TBD	mV
High-level output voltage(2) V_{ODH}	Low swing LVDS		+200		mV
Low-level output voltage(2) V_{ODL}	Low swing LVDS		–200		mV
Output common-mode voltage V_{OCM}		TBD	1.15	TBD	V

(1) SDATA and SCLK have an internal 200kΩ pull-down resistor.
(2) With an external 100Ω termination.

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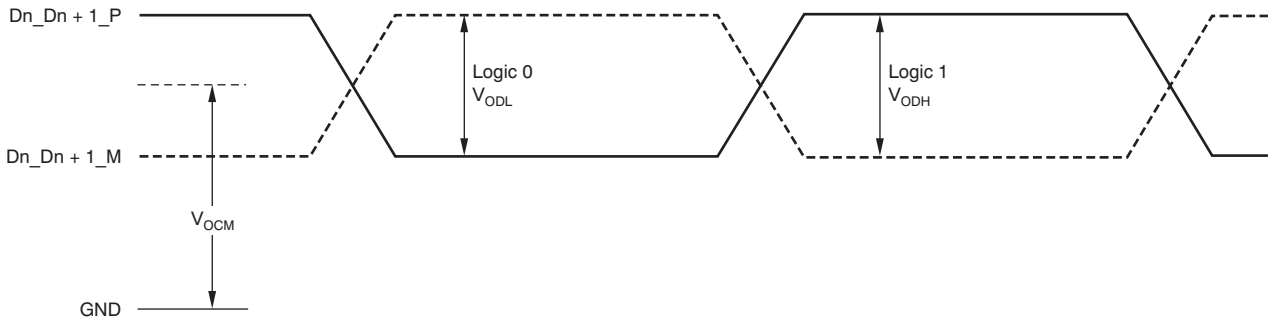
TIMING CHARACTERISTICS



(1) With external 100Ω termination.

Figure 3. LVDS Output Voltage Levels

TIMING REQUIREMENTS: LVDS and CMOS Modes(1)

Typical values are at +25°C, AVDD = 1.8V, DRVDD = 1.8V, sampling frequency = 250 MSPS, sine wave input clock, C_{LOAD} = 5pF(2), R_{LOAD} = 100Ω(3), no internal termination, and low-speed mode disabled, unless otherwise noted.
Minimum and maximum values are across the full temperature range: T_{MIN} = –40°C to T_{MAX} = +85°C, AVDD = 1.8V, DRVDD = 1.7V to 1.9V.

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
T_A	Aperture delay		TBD	TBD	TBD	ns
	Variation of aperture delay	Between two devices at the same temperature and DRVDD supply		±TBD		ps
T_J	Aperture jitter			140		f_S rms
	Wakeup time	Time to valid data after coming out of STANDBY mode		TBD	TBD	µs
		Time to valid data after coming out of PDN GLOBAL mode		TBD	TBD	µs
		Time to valid data after stopping and restarting the input clock		TBD	TBD	µs
	ADC latency(4)	Low-latency mode (default after reset)		TBD		Clock cycles
		Low-latency mode disabled (gain enabled, offset correction disabled)		TBD		Clock cycles
		Low-latency mode disabled (gain and offset correction enabled)		TBD		Clock cycles
DDR LVDS MODE(5)						
t_{SU}	Data setup time (5)	Data valid(6) to zero-crossing of CLKOUTP	TBD	1.1		ns
t_H	Data hold time (5)	Zero-crossing of CLKOUTP to data becoming invalid(6)	TBD	0.75		ns
t_{PDI}	Clock propagation delay	Input clock rising edge cross-over to output clock rising edge cross-over *1MSPS ≤ sampling frequency ≤ 250MSPS*	TBD	4	TBD	ns
	Variation of t_{PDI}	Between two devices at the same temperature and DRVDD supply		±TBD		ns

(1) Timing parameters are ensured by design and characterization but are not production tested.
(2) C_{LOAD} is the effective external single-ended load capacitance between each output pin and ground.
(3) R_{LOAD} is the differential load resistance between the LVDS output pair.
(4) At higher frequencies, t_{PDI} is greater than one clock period and overall latency = ADC latency + 1.
(5) Measurements are done with a transmission line of 100Ω characteristic impedance between the device and the load. Setup and hold time specifications take into account the effect of jitter on the output data and clock.
(6) Data valid refers to a logic high of 1.26V and a logic low of 0.54V.

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TIMING REQUIREMENTS: LVDS and CMOS Modes (1) (continued)

Typical values are at +25°C, AVDD = 1.8V, DRVDD = 1.8V, sampling frequency = 250 MSPS, sine wave input clock, C_{LOAD} = 5pF (2), R_{LOAD} = 100Ω (3), no internal termination, and low-speed mode disabled, unless otherwise noted.
Minimum and maximum values are across the full temperature range: T_{MIN} = –40°C to T_{MAX} = +85°C, AVDD = 1.8V, DRVDD = 1.7V to 1.9V.

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
DDR LVDS MODE (continued)						
	LVDS bit clock duty cycle	Duty cycle of differential clock, (CLKOUTP – CLKOUTM) *TBDMSPS ≤ sampling frequency ≤ 250MSPS*	TBD	47	TBD	%
t_{RISE}, t_{FALL}	Data rise time, Data fall time	Rise time measured from –100mV to +100mV Fall time measured from +100mV to –100mV *1MSPS ≤ sampling frequency ≤ 250MSPS*		0.11		ns
$t_{CLKRISE}$, $t_{CLKFALL}$	Output clock rise time, Output clock fall time	Rise time measured from –100mV to +100mV Fall time measured from +100mV to –100mV *1MSPS ≤ sampling frequency ≤ 250MSPS*		0.14		ns
t_{OE}	Output enable (OE) to data delay	Time to valid data after OE becomes active		TBD		ns
PARALLEL CMOS MODE (7)						
t_{START}	Input clock to data delay	Input clock rising edge cross-over to start of data valid (8)		TBD	TBD	ns
t_{DV}	Data valid time	Time interval of valid data (8)	TBD	TBD		ns
t_{PDI}	Clock propagation delay	Input clock rising edge cross-over to output clock rising edge cross-over *1MSPS ≤ sampling frequency ≤ 150MSPS*		5.4		ns
	Variation of t_{PDI}	Between two devices at the same temperature and DRVDD supply		±TBD		ns
	Output clock duty cycle	Duty cycle of output clock, CLKOUT *TBD MSPS ≤ sampling frequency ≤ 150MSPS*		52		%
t_{RISE}, t_{FALL}	Data rise time, Data fall time	Rise time measured from 20% to 80% of DRVDD Fall time measured from 80% to 20% of DRVDD *1 ≤ sampling frequency ≤ 250MSPS*		TBD		ns
$t_{CLKRISE}$, $t_{CLKFALL}$	Output clock rise time, Output clock fall time	Rise time measured from 20% to 80% of DRVDD Fall time measured from 80% to 20% of DRVDD *1 ≤ sampling frequency ≤ 150MSPS*		TBD		ns
t_{OE}	Output enable (OE) to data delay	Time to valid data after OE becomes active		TBD	TBD	ns

(7) For f_S > TBDMSPS, it is recommended to use an external clock for data capture instead of the device output clock signal (CLKOUT).
(8) Data valid refers to a logic high of 1.26V and a logic low of 0.54V.

PRODUCT PREVIEW

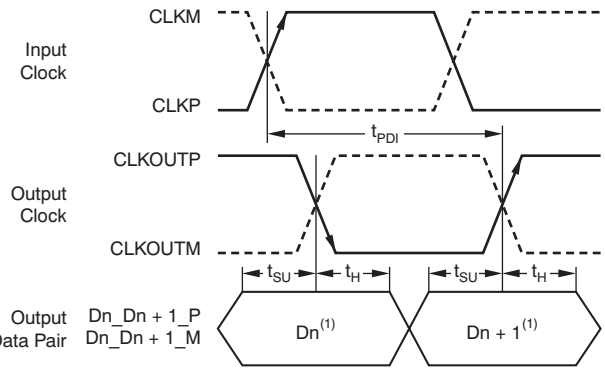
Table 2. LVDS Timing Across Sampling Frequencies

SAMPLING FREQUENCY (MSPS)	SETUP TIME (ns)			HOLD TIME (ns)		
	MIN	TYP	MAX	MIN	TYP	MAX
230	TBD	1.25		TBD	0.75	
200	TBD	1.50		TBD	0.75	
185	TBD	1.75		TBD	0.75	
150	TBD	2.40		TBD	0.75	
125	TBD	3.00		TBD	0.75	

Table 3. CMOS Timing Across Sampling Frequencies

SAMPLING FREQUENCY (MSPS)	TIMING SPECIFIED WITH RESPECT TO INPUT CLOCK					
	t_{START} (ns)			DATA VALID TIME (ns)		
	MIN	TYP	MAX	MIN	TYP	MAX
210		TBD	TBD	TBD	TBD	
190		TBD	TBD	TBD	TBD	
170		TBD	TBD	TBD	TBD	
160		TBD	TBD	TBD	TBD	
SAMPLING FREQUENCY (MSPS)	**TIMING SPECIFIED WITH RESPECT TO CLKOUT**					
	SETUP TIME (ns)			**HOLD TIME (ns)**		
	MIN	**TYP**	**MAX**	**MIN**	**TYP**	**MAX**
150	TBD	2.90		TBD	3.4	
125	TBD	3.55		TBD	3.1	

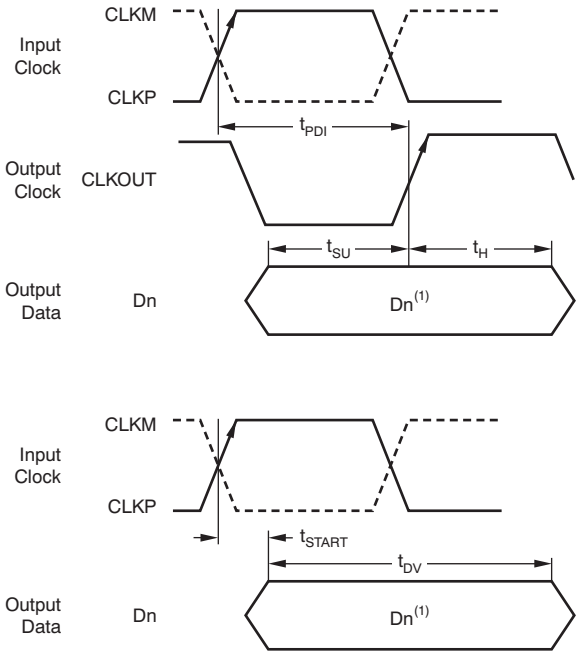
Figure 4. Latency Diagram



(1) Dn = bits D0, D2, D4, etc. Dn + 1 = Bits D1, D3, D5, etc.

Figure 5. LVDS Mode Timing

PRODUCT PREVIEW



Dn = bits D0, D1, D2, etc.

Figure 6. CMOS Mode Timing

PRODUCT PREVIEW

DEVICE CONFIGURATION

The ADS414x/2x have several modes that can be configured using a serial programming interface, as described in Table 4, Table 5, and Table 6. In addition, the devices have two dedicated parallel pins for quickly configuring commonly used functions. The parallel pins are DFS (analog 4-level control pin) and OE (digital control pin). The analog control pins can be easily configured using a simple resistor divider (with **TBD**% tolerance resistors).

Table 4. DFS: Analog Control Pin

VOLTAGE APPLIED ON DFS	DESCRIPTION (Data Format/Output Interface)
0, +100mV/–0mV	Twos complement/DDR LVDS
(3/8) AVDD ± 100mV	Twos complement/parallel CMOS
(5/8) AVDD ± 100mV	Straight binary/parallel CMOS
AVDD, +0mV/–100mV	Straight binary/DDR LVDS

Table 5. OE: Digital Control Pin

VOLTAGE APPLIED ON OE	DESCRIPTION
0	Output data buffers disabled
AVDD	Output data buffers enabled

When the serial interface is not used, the SDATA pin can also be used as a digital control pin to place the device in standby mode. To enable this, the RESET pin must be tied high.

Table 6. SDATA: Digital Control Pin

VOLTAGE APPLIED ON SDATA	DESCRIPTION
0	Normal operation
Logic high	Device enters standby

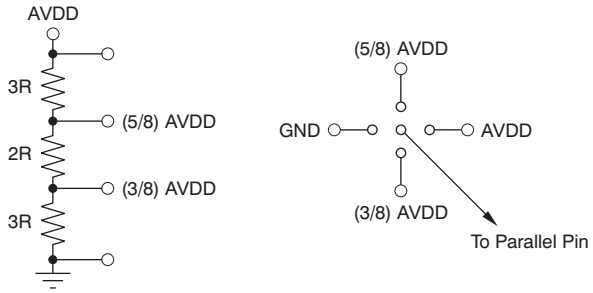


Figure 7. Simplified Diagram to Configure DFS Pin

PRODUCT PREVIEW

SERIAL INTERFACE

The analog-to-digital converter (ADC) has a set of internal registers that can be accessed by the serial interface formed by the SEN (serial interface enable), SCLK (serial interface clock), and SDATA (serial interface data) pins. Serial shift of bits into the device is enabled when SEN is low. Serial data SDATA are latched at every falling edge of SCLK when SEN is active (low). The serial data are loaded into the register at every 16th SCLK falling edge when SEN is low. In case the word length exceeds a multiple of 16 bits, the excess bits are ignored. Data can be loaded in multiples of 16-bit words within a single active SEN pulse. The first eight bits form the register address and the remaining eight bits are the register data. The interface can work with SCLK frequency from 20MHz down to very low speeds (a few Hertz) and also with non-50% SCLK duty cycle.

Register Initialization

After power-up, the internal registers must be initialized to the default values. This initialization can be accomplished in one of two ways:

1. Either through hardware reset by applying a high pulse on RESET pin (of width greater than 10ns), as shown in Figure 8; or
2. By applying a software reset. When using the serial interface, set the RESET bit (D7 in register 0x00) high. This setting initializes the internal registers to the default values and then self-resets the RESET bit low. In this case, the RESET pin is kept low.

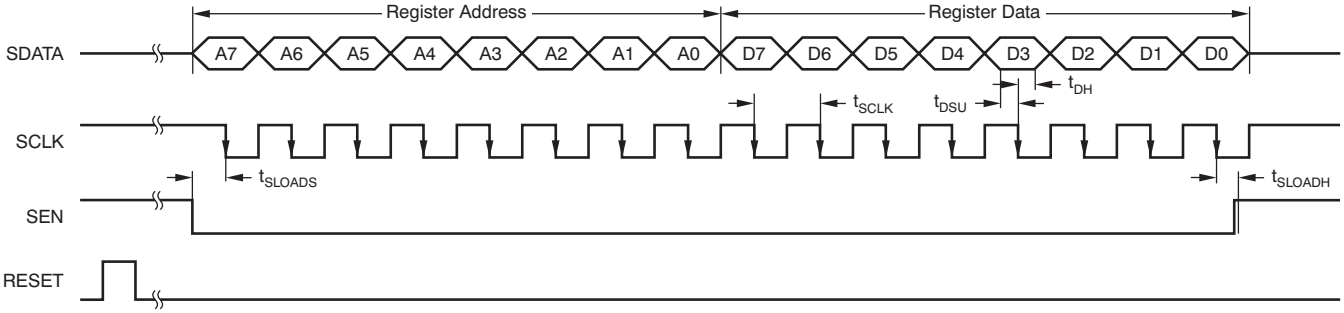


Figure 8. Serial Interface Timing

SERIAL INTERFACE TIMING CHARACTERISTICS

Typical values at +25°C, minimum and maximum values across the full temperature range: T_{MIN} = –40°C to T_{MAX} = +85°C, AVDD = 1.8V, and DRVDD = 1.8V, unless otherwise noted.

PARAMETER		MIN	TYP	MAX	UNIT
f_{SCLK}	SCLK frequency (equal to $1/t_{SCLK}$)	> DC			MHz
t_{SLOADS}	SEN to SCLK setup time	TBD			ns
t_{SLOADH}	SCLK to SEN hold time	TBD			ns
t_{DS}	SDATA setup time	TBD			ns
t_{DH}	SDATA hold time	TBD			ns

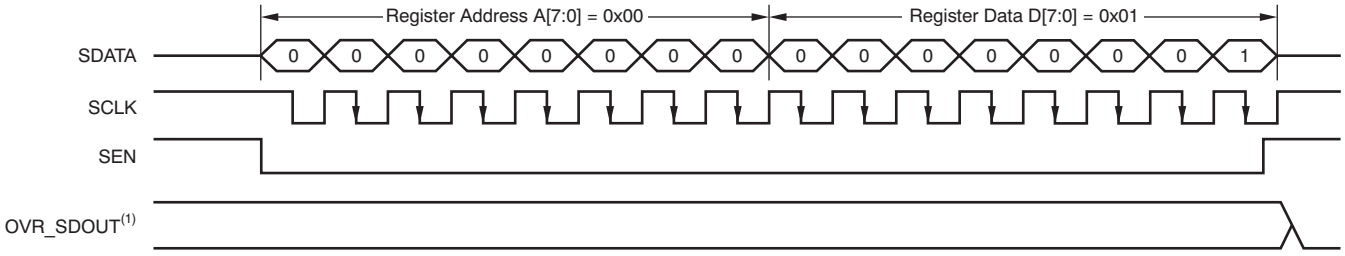
PRODUCT PREVIEW

Serial Register Readout

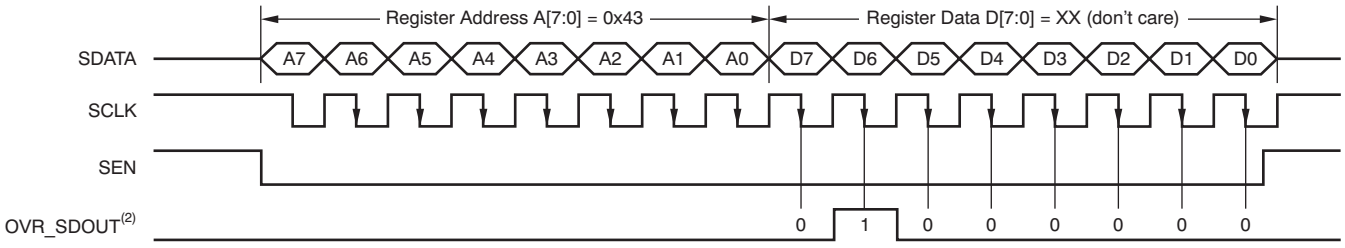
The serial register readout function allows the contents of the internal registers to be read back on the OVR_SDOUT pin. This readback may be useful as a diagnostic check to verify the serial interface communication between the external controller and the ADC.

After power-up and device reset, the OVR_SDOUT pin functions as an over-range indicator pin by default. When the readout mode is enabled, OVR_SDOUT outputs the contents of the selected register serially:

1. Set the READOUT register bit to '1'. This setting puts the device in serial readout mode and disables any further writes to the internal registers **except** the register at address 0. Note that the READOUT bit itself is also located in register 0. The device can exit readout mode by writing READOUT = 0. Only the contents of the register at address 0 cannot be read in the register readout mode.
2. Initiate a serial interface cycle specifying the address of the register (A7 to A0) whose content has to be read.
3. The device serially outputs the contents (D7 to D0) of the selected register on the OVR_SDOUT pin.
4. The external controller can latch the contents at the falling edge of SCLK.
5. To exit the serial readout mode, the reset register bit READOUT = 0 enables writes into all registers of the device. At this point, the OVR_SDOUT pin becomes an over-range indicator pin.



a) Enable Serial Readout (READOUT = 1)



b) Read Contents of Register 0x43. This Register Has Been Initialized with 0x40 (device is put in global power-down mode).

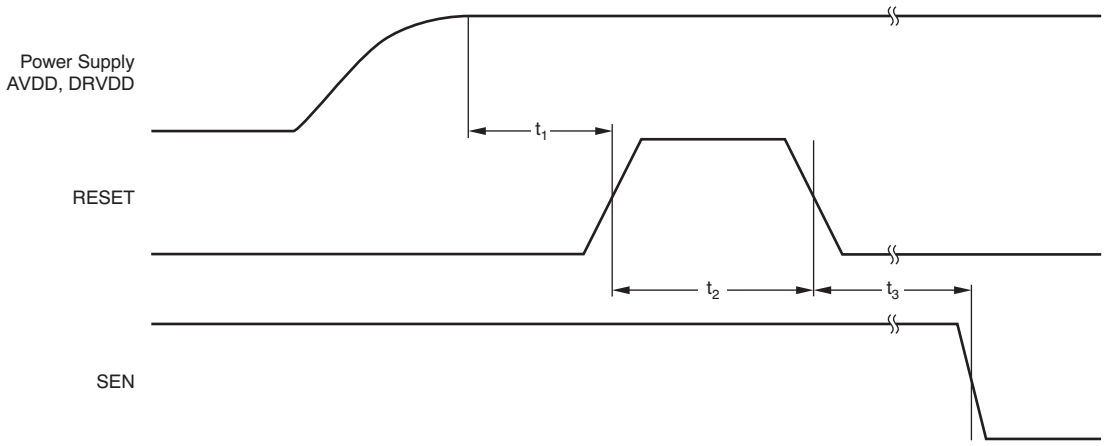
(1) The OVR_SDOUT pin finctions as OVR (READOUT = 0).

(2) The OVR_SDOUT pin finctions as a serial readout (READOUT = 1).

Figure 9. Serial Readout Timing Diagram

PRODUCT PREVIEW

RESET TIMING CHARACTERISTICS



NOTE: A high pulse on the RESET pin is required in the serial interface mode in case of initialization through hardware reset. For parallel interface operation, RESET must be permanently tied high.

Figure 10. Reset Timing Diagram

RESET TIMING REQUIREMENTS

Typical values at +25°C and minimum and maximum values across the full temperature range: T_{MIN} = –40°C to T_{MAX} = +85°C, unless otherwise noted.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_1	Power-on delay	Delay from power-up of AVDD and DRVDD to RESET pulse active		TBD		ms
t_2	Reset pulse width	Pulse width of active RESET signal that resets the serial registers		TBD		ns
				TBD		µs
t_3		Delay from RESET disable to SEN active		TBD		ns

PRODUCT PREVIEW

SERIAL REGISTER MAP

Table 7 summarizes the functions supported by the serial interface.

Table 7. Serial Interface Register Map(1)

REGISTER ADDRESS	DEFAULT VALUE AFTER RESET	REGISTER DATA							
A[7:0] (Hex)	D[7:0] (Hex)	D7	D6	D5	D4	D3	D2	D1	D0
00	00	0	0	0	0	0	0	RESET	READOUT
25	00	GAIN				DISABLE GAIN	TEST PATTERNS		
26	00	0	0	0	0	0	0	LVDS CLKOUT STRENGTH	LVDS DATA STRENGTH
3D	00	DATA FORMAT		EN OFFSET CORR	0	0	0	0	0
3F	00	CUSTOM PATTERN HIGH D[13:6]							
40	00	CUSTOM PATTERN D[5:0]						0	0
41	00	LVDS CMOS		CMOS CLKOUT STRENGTH		EN CLKOUT RISE	CLKOUT RISE POSN		EN CLKOUT FALL
42	00	CLKOUT FALL POSN		0	0	0	STBY	0	0
43	00	0	PDN GLOBAL	0	PDN OBUF	0	0	0	0
BF	00	OFFSET PEDESTAL						0	0
CF	00	FREEZE OFFSET CORR	BYPASS OFFSET CORR	OFFSET CORR TIME CONSTANT				0	0

(1) Multiple functions in a register can be programmed in a single write operation.

DESCRIPTION OF SERIAL REGISTERS

Register Address 00 (Default = 00h)

7	6	5	4	3	2	1	0
0	0	0	0	0	0	RESET	READOUT

Bits[7:2] Always write '0'

Bit 1 RESET: Software reset applied

This bit resets all internal registers to the default values and self-clears to 0 (default = 1).

Bit 0 READOUT: Serial readout

This bit sets the serial readout of the registers.
0 = Serial readout of registers disabled; the OVR_SDOUT pin functions as an over-voltage indicator.
1 = Serial readout enabled; the OVR_SDOUT pin functions as a serial data readout.

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Register Address 25 (Default = 00h)

7	6	5	4	3	2	1	0
GAIN				DISABLE GAIN	TEST PATTERNS		

Bits[7:4] GAIN: Gain programmability

These bits set the gain programmability in 0.5dB steps.
0000 = 0dB gain (default after reset)
0001 = 0.5dB gain
0010 = 1.0dB gain
0011 = 1.5dB gain
0100 = 2.0dB gain
0101 = 2.5dB gain
0110 = 3.0dB gain
0111 = 3.5dB gain
1000 = 4.0dB gain
1001 = 4.5dB gain
1010 = 5.0dB gain
1011 = 5.5dB gain
1100 = 6dB gain

Bit 3 DISABLE GAIN: Gain setting

This bit sets the gain.
0 = Gain enabled; gain is set by the GAIN bits only if low-latency mode is disabled
1 = Gain disabled

Bits[2:0] TEST PATTERNS: Data capture

These bits verify data capture.
000 = Normal operation
001 = Outputs all 0s
010 = Outputs all 1s
011 = Outputs toggle pattern

In the ADS4146/49, output data D[13:0] is an alternating sequence of *0101010101010* and *1010101010101*.
In the ADS4126/29, output data D[11:0] is an alternating sequence of *0101010101010* and *1010101010101*.

100 = Outputs digital ramp

In ADS4149/46, output data increments by one LSB (14-bit) every clock cycle from code 0 to code 16383
In ADS4129/26, output data increments by one LSB (12-bit) every 4th clock cycle from code 0 to code 4095

101 = Output custom pattern (use registers 0x3F and 0x40 for setting the custom pattern)
110 = Unused
111 = Unused

PRODUCT PREVIEW

Register Address 26 (Default = 00h)

7	6	5	4	3	2	1	0
0	0	0	0	0	0	LVDS CLKOUT STRENGTH	LVDS DATA STRENGTH

Bits[7:2] Always write '0'

Bit 1 LVDS CLKOUT STRENGTH: LVDS output clock buffer strength

This bit determines the external termination to be used with the LVDS output clock buffer.
0 = 100Ω external termination (default strength)
1 = 50Ω external termination (2x strength)

Bit 0 LVDS DATA STRENGTH: LVDS data buffer strength

This bit determines the external termination to be used with all of the LVDS data buffers.
0 = 100Ω external termination (default strength)
1 = 50Ω external termination (2x strength)

Register Address 3D (Default = 00h)

7	6	5	4	3	2	1	0
DATA FORMAT		EN OFFSET CORR	0	0	0	0	0

Bits[7:6] DATA FORMAT: Data format selection

These bits selects the data format.
00 = The DFS pin controls data format selection
10 = Twos complement
11 = Offset binary

Bit 5 ENABLE OFFSET CORR: Offset correction setting

This bit sets the offset correction.
0 = Offset correction disabled
1 = Offset correction enabled

Bits[4:0] Always write '0'

Register Address 3F (Default = 00h)

7	6	5	4	3	2	1	0
CUSTOM PATTERN HIGH D13	CUSTOM PATTERN HIGH D12	CUSTOM PATTERN HIGH D11	CUSTOM PATTERN HIGH D10	CUSTOM PATTERN HIGH D9	CUSTOM PATTERN HIGH D8	CUSTOM PATTERN HIGH D7	CUSTOM PATTERN HIGH D6

Bits[7:0] CUSTOM PATTERN

These bits set the custom pattern.

Register Address 40 (Default = 00h)

7	6	5	4	3	2	1	0
CUSTOM PATTERN D5	CUSTOM PATTERN D4	CUSTOM PATTERN D3	CUSTOM PATTERN D2	CUSTOM PATTERN D1	CUSTOM PATTERN D0	0	0

Bits[7:2] CUSTOM PATTERN

These bits set the custom pattern.

Bits[1:0] Always write '0'

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Register Address 41 (Default = 00h)

7	6	5	4	3	2	1	0
LVDS CMOS		CMOS CLKOUT STRENGTH		EN CLKOUT RISE	CLKOUT RISE POSN		EN CLKOUT FALL

Bits[7:6] LVDS CMOS: Interface selection

These bits select the interface.
00 = The DFS pin controls the selection of either LVDS or CMOS interface
01 = DDR LVDS interface
01 = Parallel CMOS interface

Bits[5:4] CMOS CLKOUT STRENGTH

Setting is TBD.

Bit 3 ENABLE CLKOUT RISE

Setting is TBD.

Bits[2:1] CLKOUT RISE POSN: CLKOUT rise control

Setting is TBD.

Bit 0 ENABLE CLKOUT FALL

Setting is TBD.

Register Address 42 (Default = 00h)

7	6	5	4	3	2	1	0
CLKOUT FALL POSN		0	0	0	STBY	0	0

Bits[7:6] CLKOUT FALL CTRL

Setting is TBD.

Bits[5:3] Always write '0'

Bit 2 STBY: Standby mode

This bet sets the standby mode.
0 = Normal operation
1 = Only the ADC and output buffers are powered down; internal reference is active; wake-up time from standby is fast

Bits[1:0] Always write '0'

Register Address 43 (Default = 00h)

7	6	5	4	3	2	1	0
0	PDN GLOBAL	0	PDN OBUF	0	0	0	0

Bit 0 Always write '0'

Bit 6 PDN GLOBAL: Power-down

This bit sets the state of operation.
0 = Normal operation
1 = Total power down; the ADC, internal references, and output buffers are powered down; slow wake-up time.

Bit 5 Always write '0'

Bit 4 PDN OBUF: Power down output buffer

This bit set the output data and clock pins.
0 = Output data and clock pins enabled
1 = Output data and clock pins powered down and put in high- impedance state

PRODUCT PREVIEW

Bits[3:0] Always write '0'

Register Address BF (Default = 00h)

7	6	5	4	3	2	1	0
OFFSET PEDESTAL						0	0

Bits[7:2] OFFSET PEDESTAL

These bits set the offset pedestal.

Bits[1:0] Always write '0'

Register Address CF (Default = 00h)

7	6	5	4	3	2	1	0
FREEZE OFFSET CORR	BYPASS OFFSET CORR	OFFSET CORR TIME CONSTANT				0	0

Bit 7 FREEZE OFFSET CORR

This bit sets the freeze offset correction.

Bit 6 BYPASS OFFSET CORR

This bit sets the bypass offset correction.

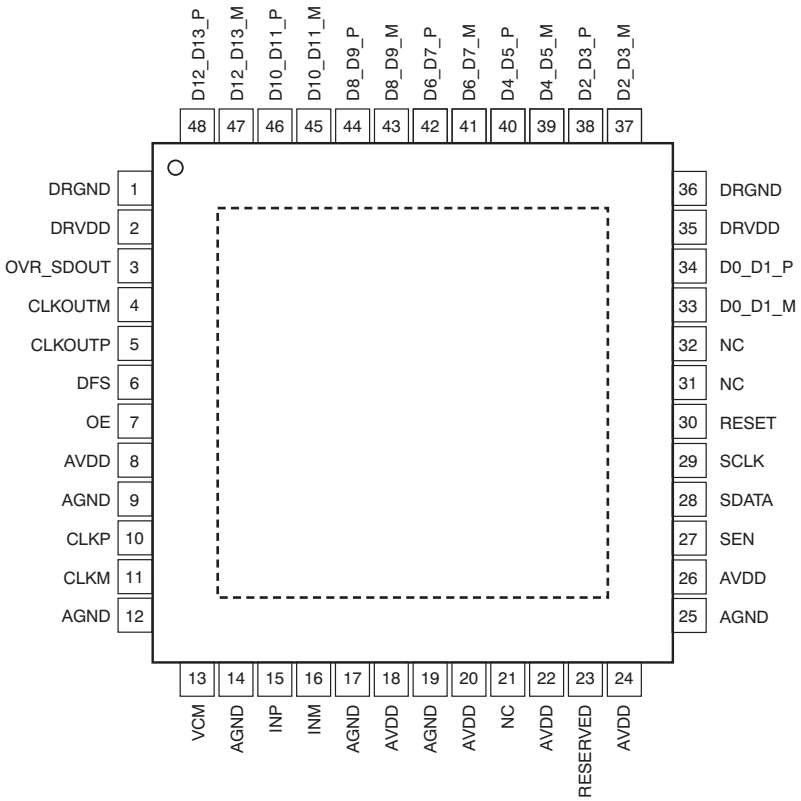
Bits[5:2] OFFSET CORR TIME CONSTANT

These bits set the offset correction time constant.

Bits[1:0] Always write '0'

PIN CONFIGURATION (LVDS MODE)

RGZ PACKAGE(1)
QFN-48
(TOP VIEW)

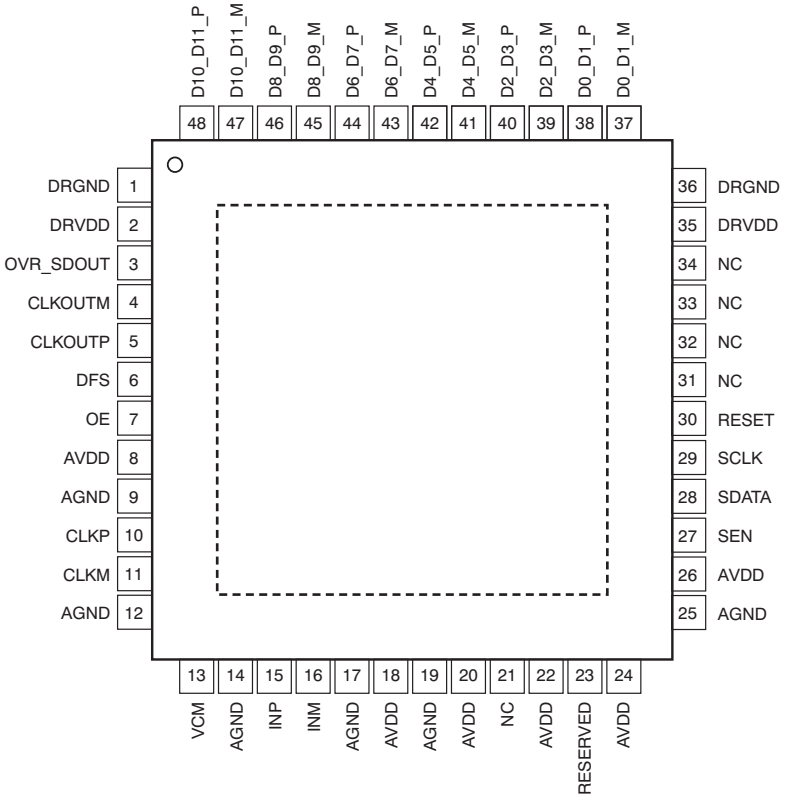


(1) The PowerPAD is connected to DRGND.

Figure 11. ADS414x LVDS Pinout

PRODUCT PREVIEW

RGZ PACKAGE(2)
QFN-48
(TOP VIEW)



(2) The PowerPAD™ is connected to DRGND.

Figure 12. ADS412x LVDS Pinout

ADS414x, ADS412x Pin Assignments (LVDS Mode)

PIN NAME	PIN NUMBER	# OF PINS	FUNCTION	DESCRIPTION
AVDD	8, 18, 20, 22, 24, 26	6	I	1.8V analog power supply
AGND	9, 12, 14, 17, 19, 25	6	I	Analog ground
CLKP	10	1	I	Differential clock input, positive
CLKM	11	1	I	Differential clock input, negative
INP	15	1	I	Differential analog input, positive
INM	16	1	I	Differential analog input, negative
VCM	13	1	O	Outputs the common-mode voltage (0.95V) that can be used externally to bias the analog input pins.
RESET	30	1	I	Serial interface RESET input. When using the serial interface mode, the internal registers must initialize through hardware RESET by applying a high pulse on this pin or by using the software reset option; refer to the *Serial Interface* section. When RESET is tied high, the internal registers are reset to the default values. In this condition, SEN can be used as an analog control pin. RESET has an internal 100kΩ pull-down resistor.
SCLK	29	1	I	Serial interface clock input; this pin has an internal 100kΩ pull-down resistor.
SDATA	28	1	I	Serial interface data input; this pin has an internal 100kΩ pull-down resistor.
SEN	27	1	I	This pin functions as a serial interface enable input when RESET is low and functions as an output clock edge control when RESET is tied high. See TBD for detailed information. This pin has an internal 100kΩ pull-up resistor to AVDD.
OE	7	1	I	Output buffer enable input, active high; this pin has an internal 100kΩ pull-up resistor to DRVDD.

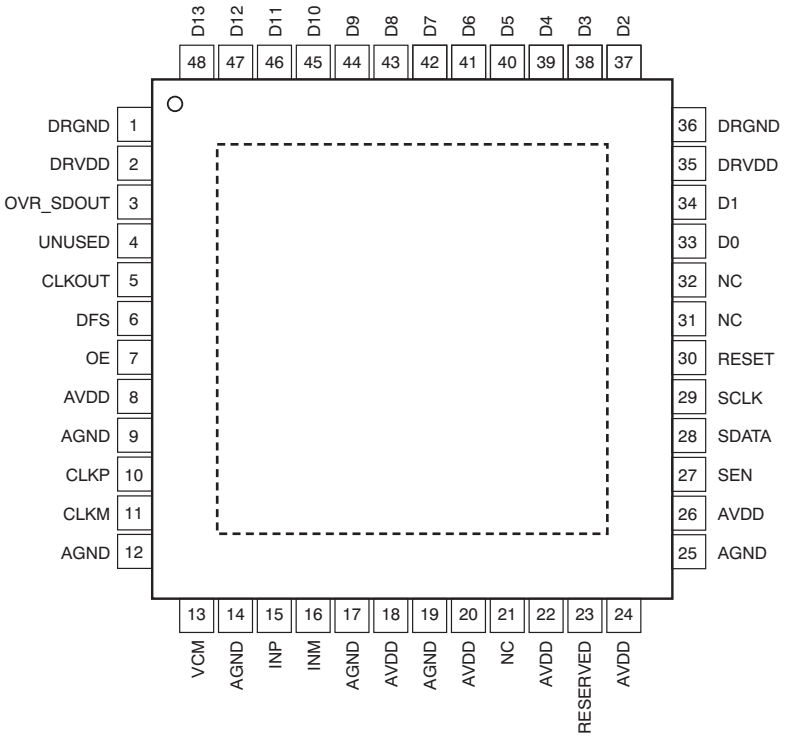
PRODUCT PREVIEW

ADS414x, ADS412x Pin Assignments (LVDS Mode) (continued)

PIN NAME	PIN NUMBER	# OF PINS	FUNCTION	DESCRIPTION
DFS	6	1	I	Data format select input. This pin sets the DATA FORMAT (twos complement or offset binary) and the LVDS/CMOS output interface type. See Table 4 for detailed information.
RESERVED	23	1	I	Digital control pin, reserved for future use
CLKOUTP	5	1	O	Differential output clock, true
CLKOUTM	4	1	O	Differential output clock, complement
D0_D1_P	Refer to Figure 11 and Figure 12	1	O	Differential output data D0 and D1 multiplexed, true
D0_D1_M	Refer to Figure 11 and Figure 12	1	O	Differential output data D0 and D1 multiplexed, complement
D2_D3_P	Refer to Figure 11 and Figure 12	1	O	Differential output data D2 and D3 multiplexed, true
D2_D3_M	Refer to Figure 11 and Figure 12	1	O	Differential output data D2 and D3 multiplexed, complement
D4_D5_P	Refer to Figure 11 and Figure 12	1	O	Differential output data D4 and D5 multiplexed, true
D4_D5_M	Refer to Figure 11 and Figure 12	1	O	Differential output data D4 and D5 multiplexed, complement
D6_D7_P	Refer to Figure 11 and Figure 12	1	O	Differential output data D6 and D7 multiplexed, true
D6_D7_M	Refer to Figure 11 and Figure 12	1	O	Differential output data D6 and D7 multiplexed, complement
D8_D9_P	Refer to Figure 11 and Figure 12	1	O	Differential output data D8 and D9 multiplexed, true
D8_D9_M	Refer to Figure 11 and Figure 12	1	O	Differential output data D8 and D9 multiplexed, complement
D10_D11_P	Refer to Figure 11 and Figure 12	1	O	Differential output data D10 and D11 multiplexed, true
D10_D11_M	Refer to Figure 11 and Figure 12	1	O	Differential output data D10 and D11 multiplexed, complement
D12_D13_P	Refer to Figure 11 and Figure 12	1	O	Differential output data D12 and D13 multiplexed, true
D12_D13_M	Refer to Figure 11 and Figure 12	1	O	Differential output data D12 and D13 multiplexed, complement
OVR_SDOUT	3	1	O	This pin functions as an out-of-range indicator after reset, when register bit READOUT = 0, and functions as a serial register readout pin when READOUT = 1.
DRVDD	2, 35	2	I	1.8V digital and output buffer supply
DRGND	1, 36, PAD	2	I	Digital and output buffer ground
NC	Refer to Figure 11 and Figure 12	—	—	Do not connect

PIN CONFIGURATION (CMOS MODE)

RGZ PACKAGE(3)
QFN-48
(TOP VIEW)

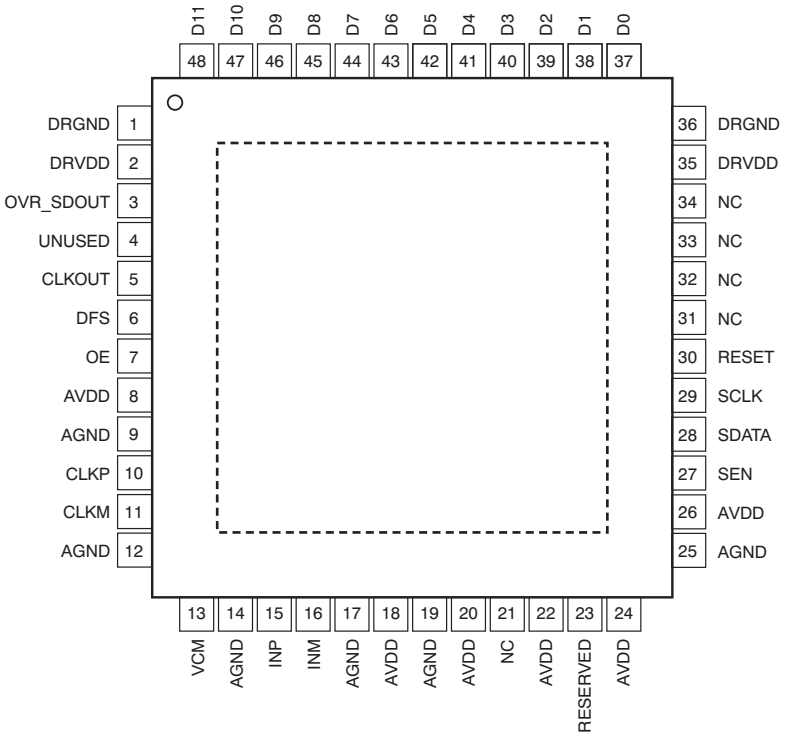


(3) The PowerPAD is connected to DRGND.

Figure 13. ADS414x CMOS Pinout

PRODUCT PREVIEW

RGZ PACKAGE(4)
QFN-48
(TOP VIEW)



(4) The PowerPAD is connected to DRGND.

Figure 14. ADS412x CMOS Pinout

ADS414x, ADS412x Pin Assignments (CMOS Mode)

PIN NAME	PIN NUMBER	# OF PINS	FUNCTION	DESCRIPTION
AVDD	8, 18, 20, 22, 24, 26	6	I	1.8V analog power supply
AGND	9, 12, 14, 17, 19, 25	6	I	Analog ground
CLKP	10	1	I	Differential clock input, positive
CLKM	11	1	I	Differential clock input, negative
INP	15	1	I	Differential analog input, positive
INM	16	1	I	Differential analog input, negative
VCM	13	1	O	Outputs the common-mode voltage (0.95V) that can be used externally to bias the analog input pins.
RESET	30	1	I	Serial interface RESET input. When using the serial interface mode, the internal registers must initialize through hardware RESET by applying a high pulse on this pin or by using the software reset option; refer to the *Serial Interface* section. When RESET is tied high, the internal registers are reset to the default values. In this condition, SEN can be used as an analog control pin. RESET has an internal 100kΩ pull-down resistor.
SCLK	29	1	I	Serial interface clock input; this pin has an internal 100kΩ pull-down resistor.
SDATA	28	1	I	Serial interface data input; this pin has an internal 100kΩ pull-down resistor.
SEN	27	1	I	This pin functions as a serial interface enable input when RESET is low and functions as an output clock edge control when RESET is tied high. See **TBD** for detailed information. This pin has an internal 100kΩ pull-up resistor to DRVDD.
OE	7	1	I	Output buffer enable input, active high; this pin has an internal 100kΩ pull-up resistor to DRVDD.
DFS	6	1	I	Data format select input. This pin sets the DATA FORMAT (twos complement or offset binary) and the LVDS/CMOS output interface type. See Table 4 for detailed information.
RESERVED	23	1	I	Digital control pin, reserved for future use

ADS414x, ADS412x Pin Assignments (CMOS Mode) (continued)

PIN NAME	PIN NUMBER	# OF PINS	FUNCTION	DESCRIPTION
CLKOUT	5	1	O	CMOS output clock
D0	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D1	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D2	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D3	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D4	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D5	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D6	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D7	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D8	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D9	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D10	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D11	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D12	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
D13	Refer to Figure 13 and Figure 14	1	O	14-bit/12-bit CMOS output data
OVR_SDOUT	3	1	O	This pin functions as an out-of-range indicator after reset, when register bit READOUT = 0, and functions as a serial register readout pin when READOUT = 1.
DRVDD	2, 35	2	I	1.8V digital and output buffer supply
DRGND	1, 36, PAD	2	I	Digital and output buffer ground
UNUSED	4	1	—	Unused pin in CMOS mode
NC	Refer to Figure 13 and Figure 14	—	—	Do not connect

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4149

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

FFT FOR 10MHz INPUT SIGNAL

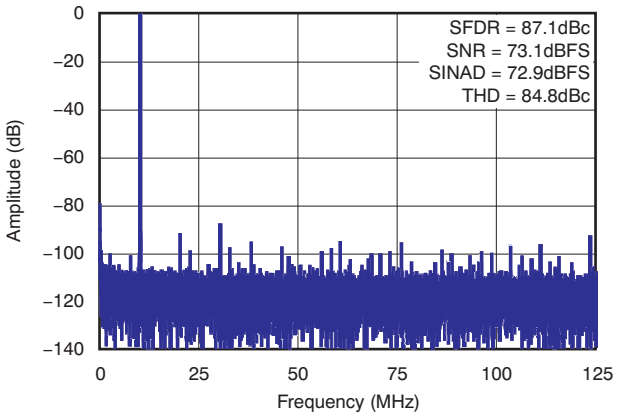


Figure 15.

FFT FOR 170MHz INPUT SIGNAL

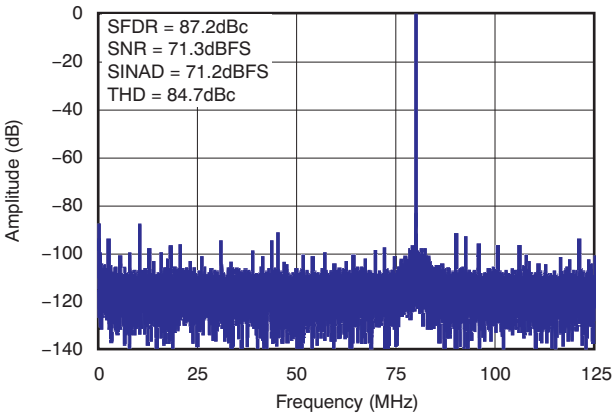


Figure 16.

FFT FOR 300MHz INPUT SIGNAL

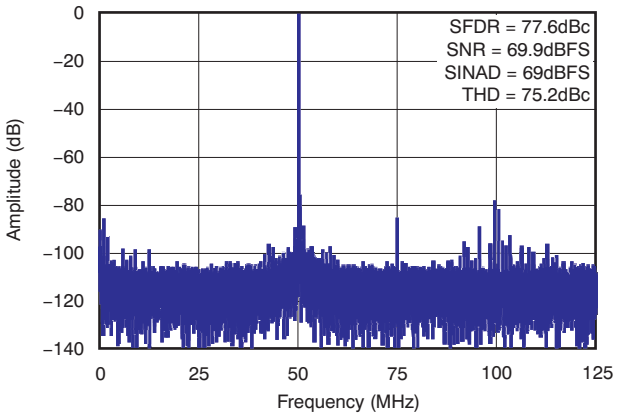


Figure 17.

FFT FOR TWO-TONE INPUT SIGNAL

Figure 18.

FFT FOR TWO-TONE INPUT SIGNAL

Figure 19.

SFDR vs INPUT FREQUENCY

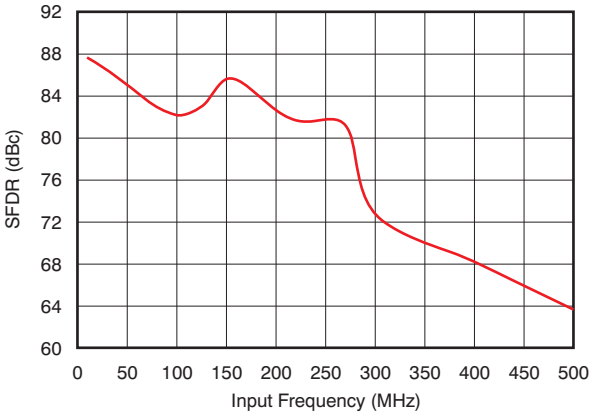


Figure 20.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4149 (continued)

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

SNR vs INPUT FREQUENCY

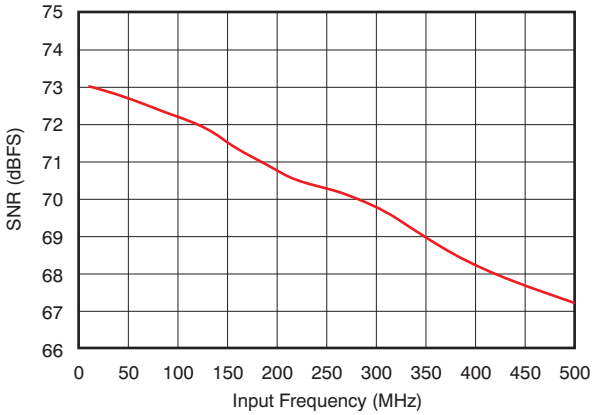


Figure 21.

SFDR vs INPUT FREQUENCY ACROSS INPUT AMPLITUDES (CMOS)

FPO

Figure 22.

SNR vs INPUT FREQUENCY ACROSS INPUT AMPLITUDES (CMOS)

FPO

Figure 23.

SFDR ACROSS GAIN

FPO

Figure 24.

SINAD ACROSS GAIN

FPO

Figure 25.

PERFORMANCE ACROSS INPUT AMPLITUDE (Single Tone)

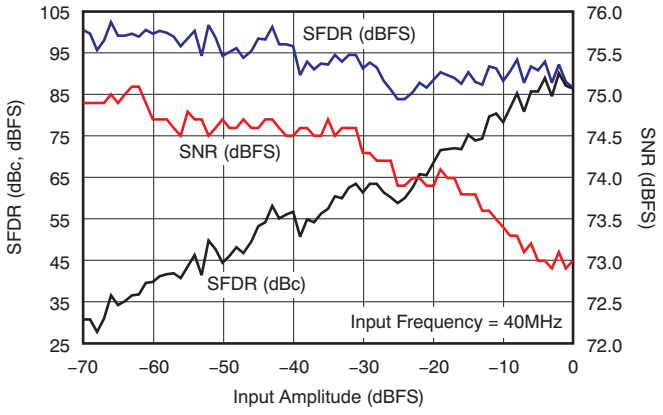


Figure 26.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4149 (continued)

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, $1.5V_{PP}$ differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

PERFORMANCE ACROSS INPUT AMPLITUDE (Single Tone)

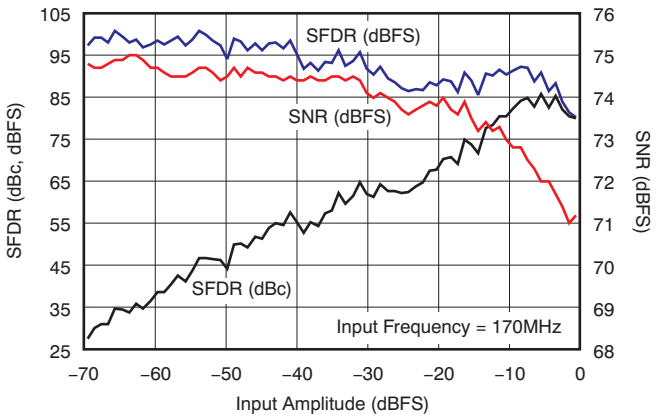


Figure 27.

PERFORMANCE vs INPUT COMMON-MODE VOLTAGE

FPO

Figure 28.

SFDR ACROSS TEMPERATURE vs AVDD SUPPLY

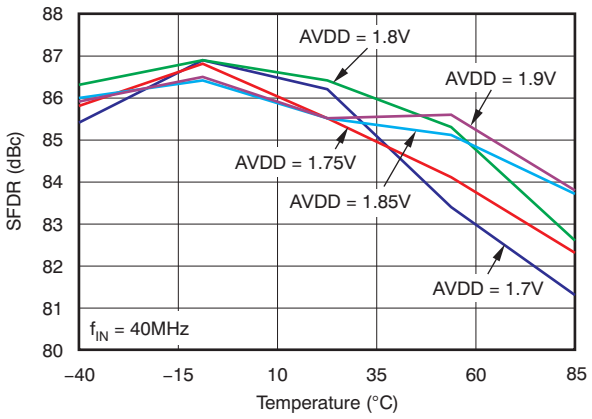


Figure 29.

SNR ACROSS TEMPERATURE vs AVDD SUPPLY

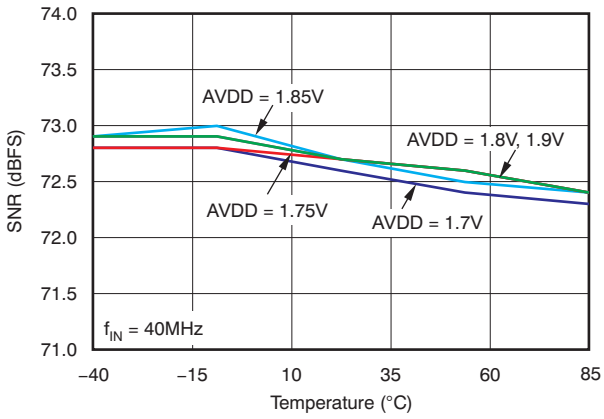


Figure 30.

PERFORMANCE ACROSS DRVDD SUPPLY VOLTAGE

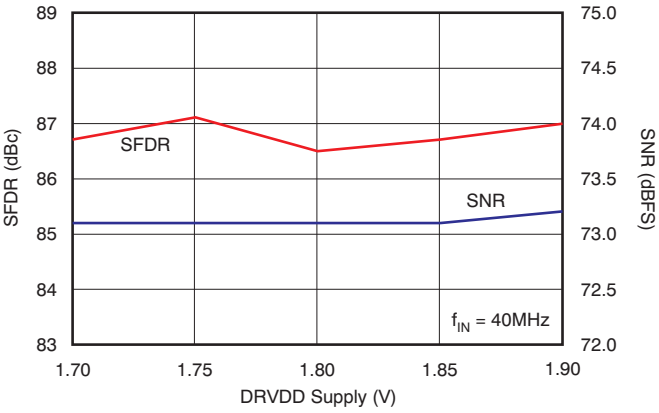


Figure 31.

PERFORMANCE ACROSS DRVDD SUPPLY VOLTAGE (CMOS)

FPO

Figure 32.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4149 (continued)

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

PERFORMANCE ACROSS INPUT CLOCK AMPLITUDE

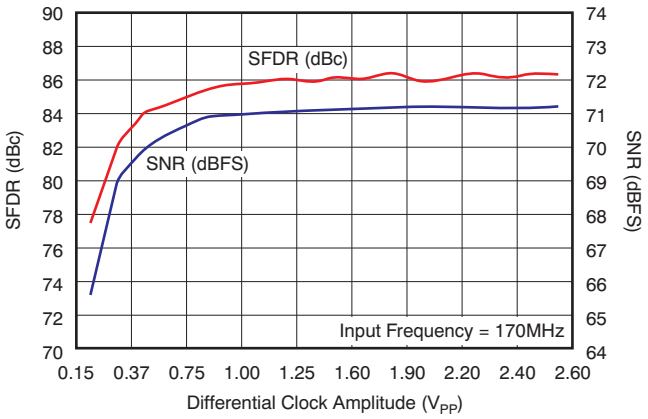


Figure 33.

PERFORMANCE ACROSS INPUT CLOCK DUTY CYCLE

Figure 34.

INTEGRAL NONLINEARITY

Figure 35.

DIFFERENTIAL NONLINEARITY

Figure 36.

OUTPUT HISTOGRAM WITH INPUTS SHORTED

Figure 37.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4146

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

FFT FOR 10MHz INPUT SIGNAL

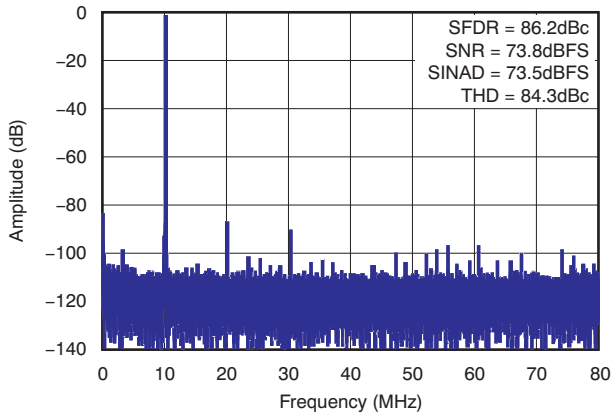


Figure 38.

FFT FOR 170MHz INPUT SIGNAL

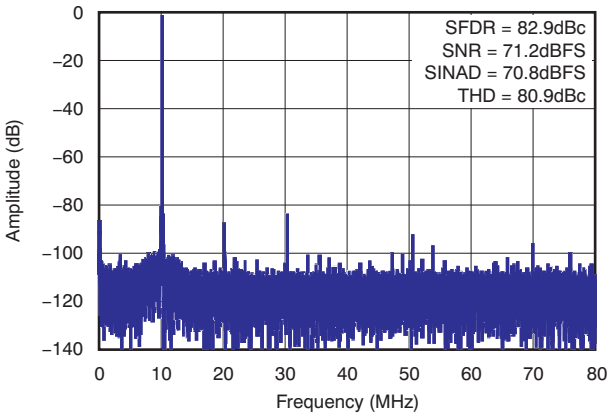


Figure 39.

FFT FOR 300MHz INPUT SIGNAL

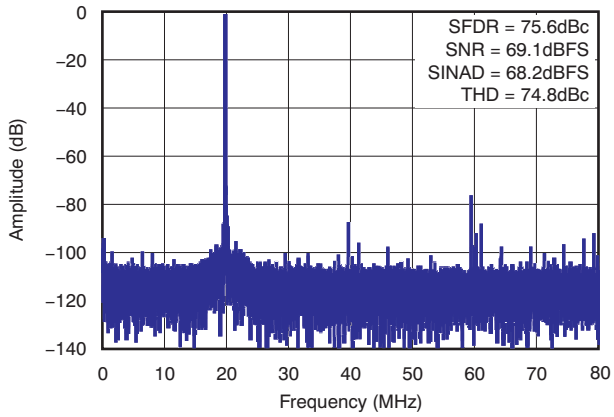


Figure 40.

FFT FOR TWO-TONE INPUT SIGNAL

Figure 41.

FFT FOR TWO-TONE INPUT SIGNAL

Figure 42.

SFDR vs INPUT FREQUENCY

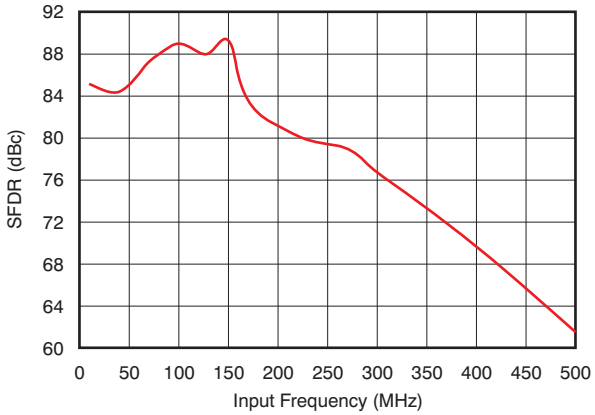


Figure 43.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4146 (continued)

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

SNR vs INPUT FREQUENCY

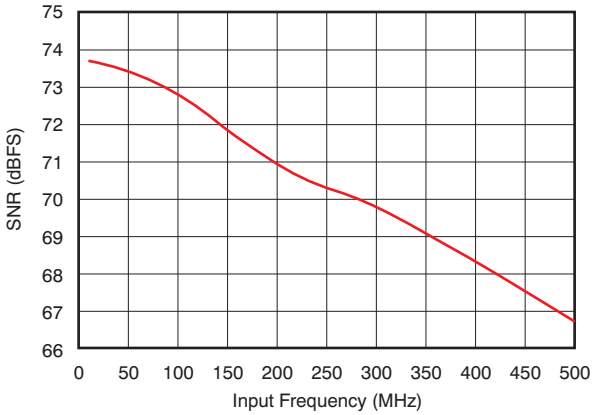


Figure 44.

SFDR vs INPUT FREQUENCY ACROSS INPUT AMPLITUDES (CMOS)

FPO

Figure 45.

SNR vs INPUT FREQUENCY ACROSS INPUT AMPLITUDES (CMOS)

FPO

Figure 46.

SFDR ACROSS GAIN

FPO

Figure 47.

SINAD ACROSS GAIN

FPO

Figure 48.

PERFORMANCE ACROSS INPUT AMPLITUDE (Single Tone)

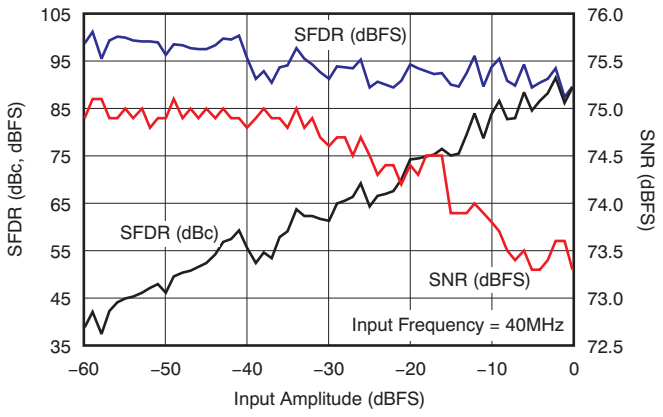


Figure 49.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4146 (continued)

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, $1.5V_{PP}$ differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

PERFORMANCE ACROSS INPUT AMPLITUDE (Single Tone)

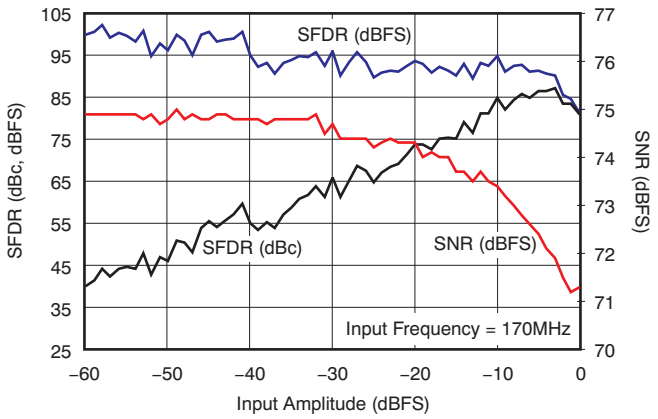


Figure 50.

PERFORMANCE vs INPUT COMMON-MODE VOLTAGE

FPO

Figure 51.

SFDR ACROSS TEMPERATURE vs AVDD SUPPLY

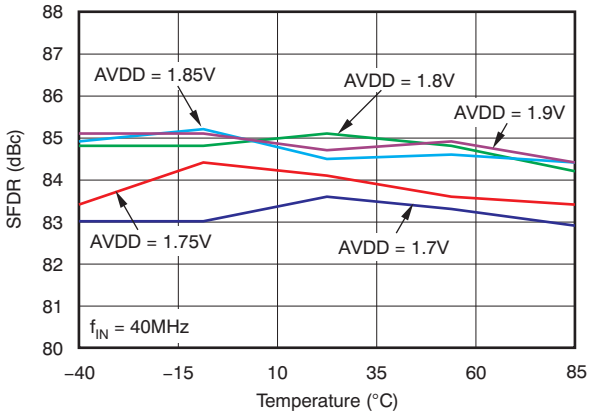


Figure 52.

SNR ACROSS TEMPERATURE vs AVDD SUPPLY

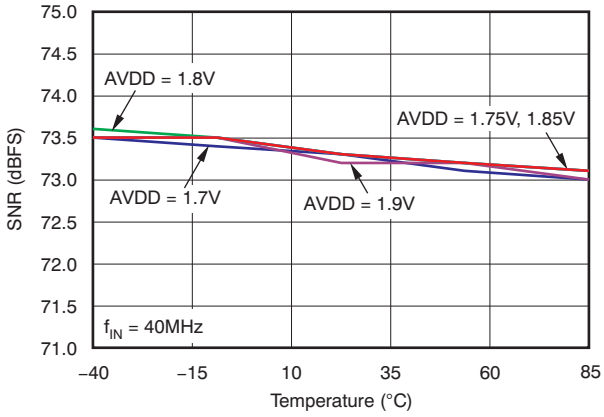


Figure 53.

PERFORMANCE ACROSS DRVDD SUPPLY VOLTAGE

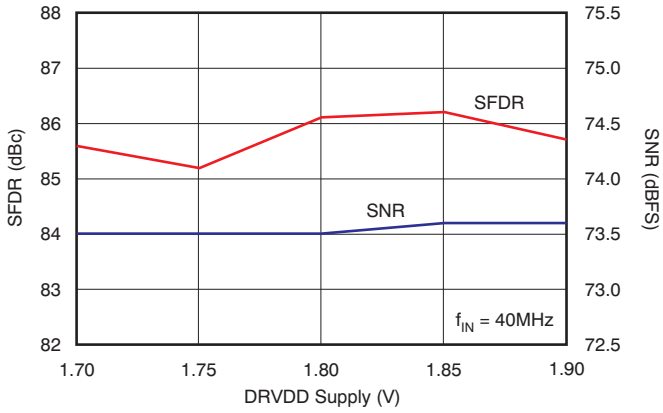


Figure 54.

PERFORMANCE ACROSS DRVDD SUPPLY VOLTAGE (CMOS)

FPO

Figure 55.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4146 (continued)

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

PERFORMANCE ACROSS INPUT CLOCK AMPLITUDE

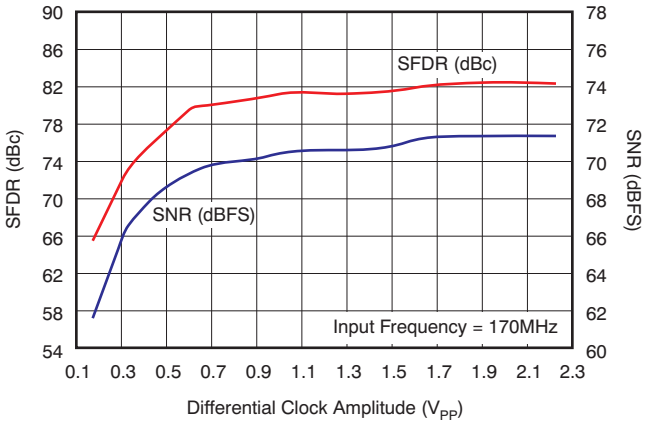


Figure 56.

PERFORMANCE ACROSS INPUT CLOCK DUTY CYCLE

Figure 57.

INTEGRAL NONLINEARITY

Figure 58.

DIFFERENTIAL NONLINEARITY

Figure 59.

OUTPUT HISTOGRAM WITH INPUTS SHORTED

Figure 60.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4129

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

FFT FOR 10MHz INPUT SIGNAL

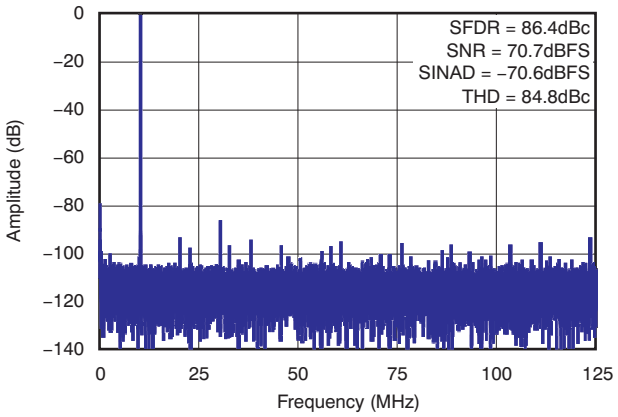


Figure 61.

FFT FOR 170MHz INPUT SIGNAL

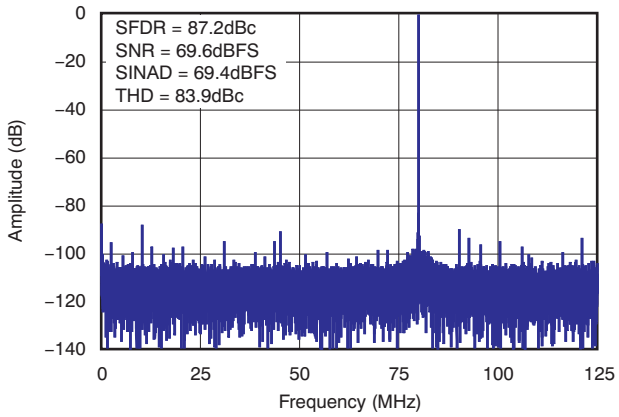


Figure 62.

FFT FOR 300MHz INPUT SIGNAL

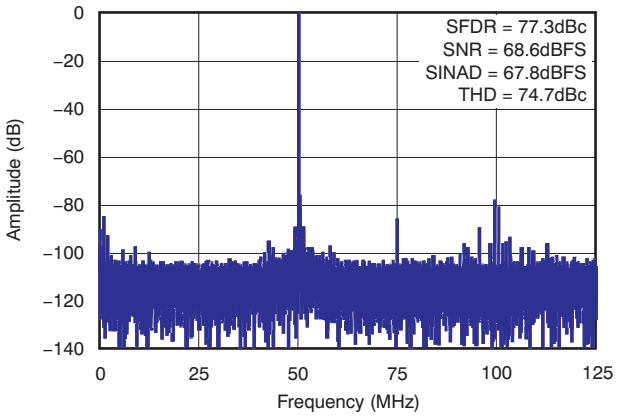


Figure 63.

FFT FOR TWO-TONE INPUT SIGNAL

Figure 64.

FFT FOR TWO-TONE INPUT SIGNAL

Figure 65.

SFDR vs INPUT FREQUENCY

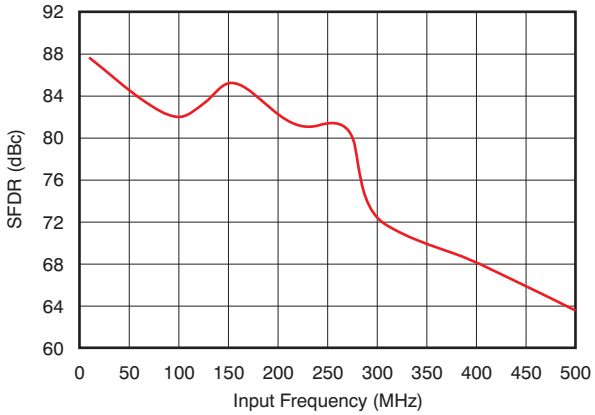


Figure 66.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4129 (continued)

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

SNR vs INPUT FREQUENCY

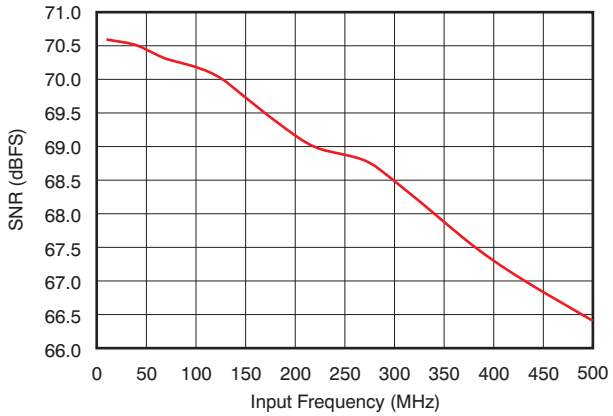


Figure 67.

SFDR vs INPUT FREQUENCY ACROSS INPUT AMPLITUDES (CMOS)

Figure 68.

SNR vs INPUT FREQUENCY ACROSS INPUT AMPLITUDES (CMOS)

Figure 69.

SFDR ACROSS GAIN

Figure 70.

SINAD ACROSS GAIN

Figure 71.

PERFORMANCE ACROSS INPUT AMPLITUDE (Single Tone)

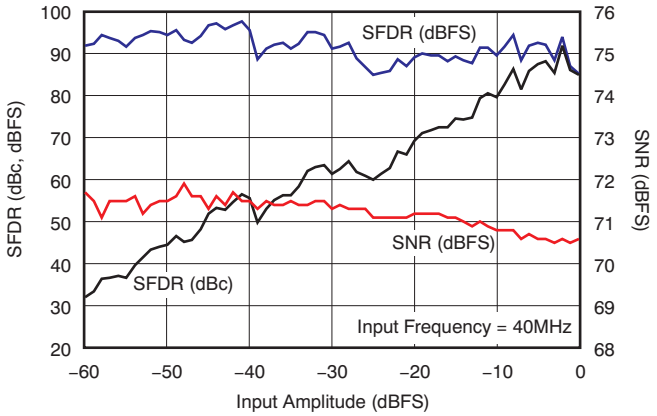


Figure 72.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4129 (continued)

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, $1.5V_{PP}$ differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

PERFORMANCE ACROSS INPUT AMPLITUDE (Single Tone)

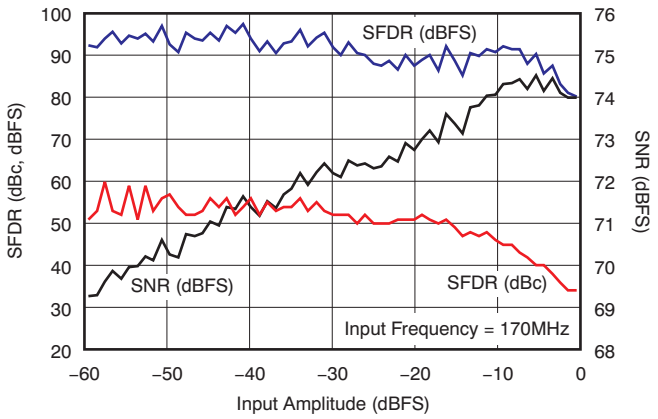


Figure 73.

PERFORMANCE vs INPUT COMMON-MODE VOLTAGE

FPO

Figure 74.

SFDR ACROSS TEMPERATURE vs AVDD SUPPLY

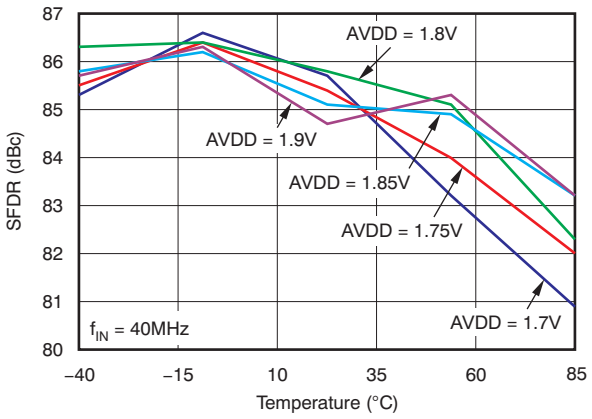


Figure 75.

SNR ACROSS TEMPERATURE vs AVDD SUPPLY

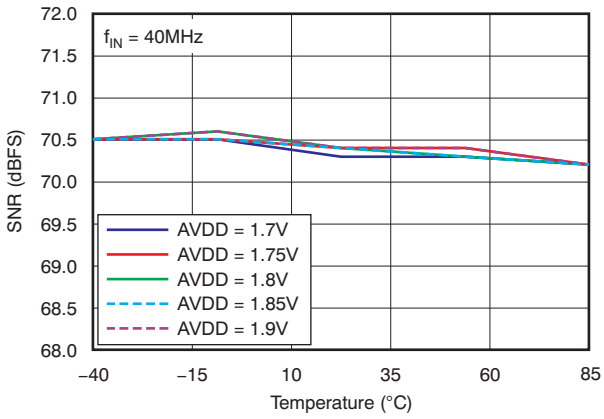


Figure 76.

PERFORMANCE ACROSS DRVDD SUPPLY VOLTAGE

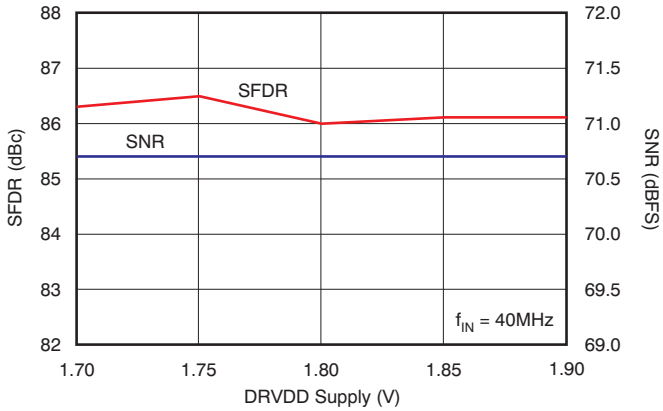


Figure 77.

PERFORMANCE ACROSS DRVDD SUPPLY VOLTAGE (CMOS)

FPO

Figure 78.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4129 (continued)

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

PERFORMANCE ACROSS INPUT CLOCK AMPLITUDE

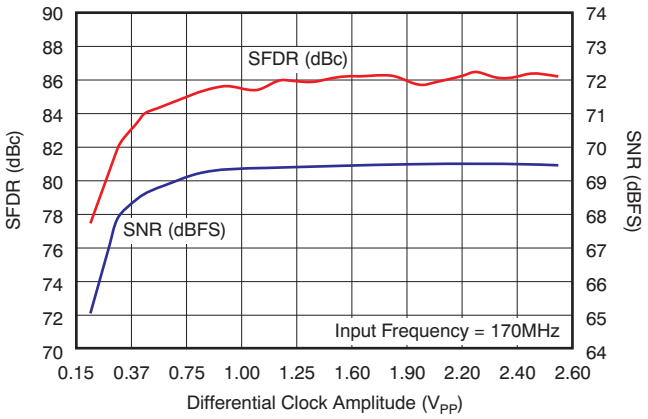


Figure 79.

PERFORMANCE ACROSS INPUT CLOCK DUTY CYCLE

Figure 80.

INTEGRAL NONLINEARITY

Figure 81.

DIFFERENTIAL NONLINEARITY

Figure 82.

OUTPUT HISTOGRAM WITH INPUTS SHORTED

Figure 83.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4126

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

FFT FOR 10MHz INPUT SIGNAL

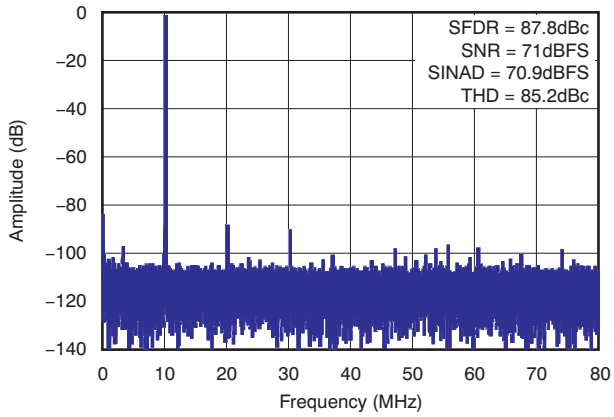


Figure 84.

FFT FOR 170MHz INPUT SIGNAL

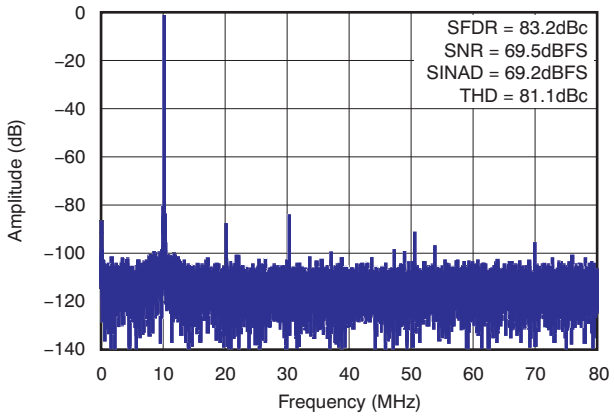


Figure 85.

FFT FOR 300MHz INPUT SIGNAL

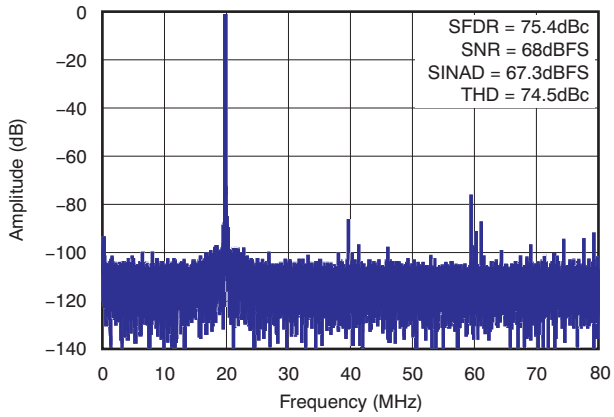


Figure 86.

FFT FOR TWO-TONE INPUT SIGNAL

Figure 87.

FFT FOR TWO-TONE INPUT SIGNAL

Figure 88.

SFDR vs INPUT FREQUENCY

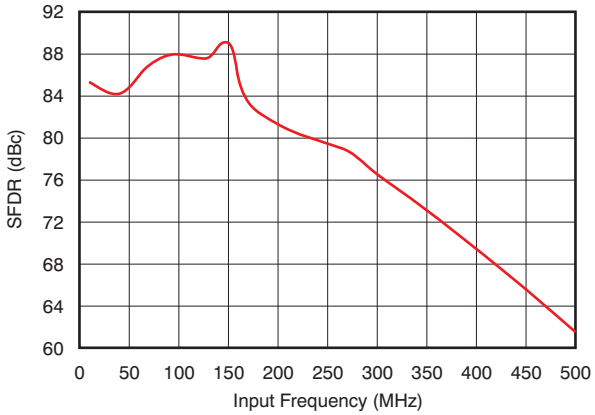


Figure 89.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4126 (continued)

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

SNR vs INPUT FREQUENCY

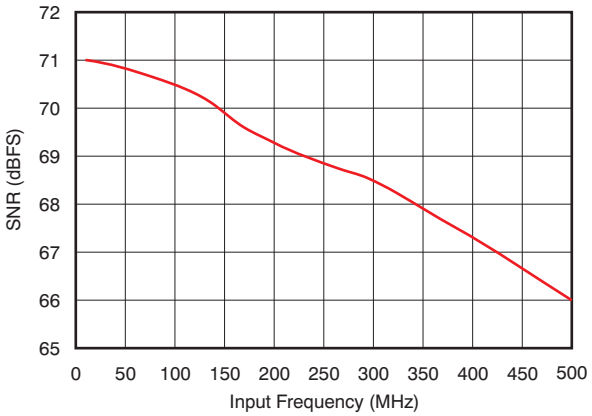


Figure 90.

SFDR vs INPUT FREQUENCY ACROSS INPUT AMPLITUDES (CMOS)

FPO

Figure 91.

SNR vs INPUT FREQUENCY ACROSS INPUT AMPLITUDES (CMOS)

FPO

Figure 92.

SFDR ACROSS GAIN

FPO

Figure 93.

SINAD ACROSS GAIN

FPO

Figure 94.

PERFORMANCE ACROSS INPUT AMPLITUDE (Single Tone)

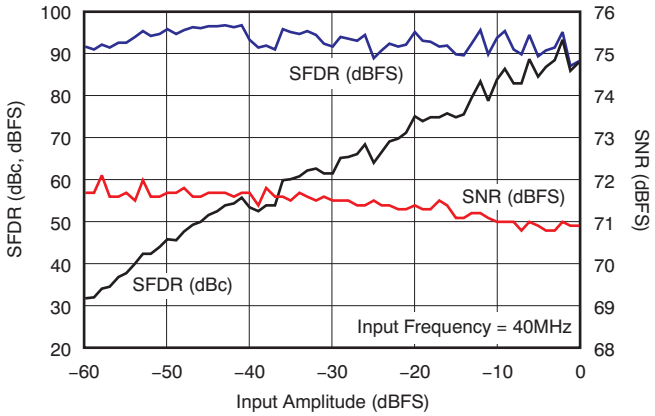


Figure 95.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4126 (continued)

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, $1.5V_{PP}$ differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

PERFORMANCE ACROSS INPUT AMPLITUDE (Single Tone)

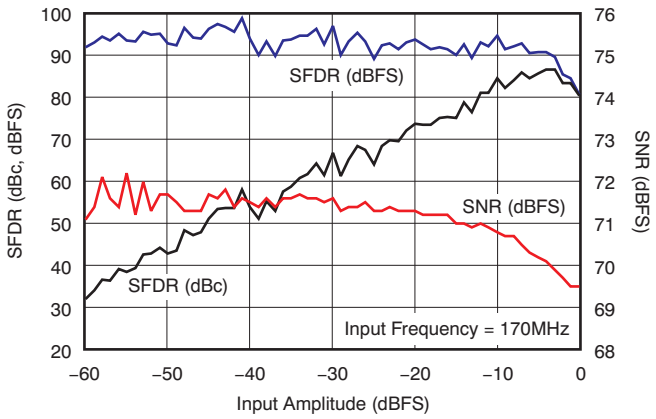


Figure 96.

PERFORMANCE vs INPUT COMMON-MODE VOLTAGE

FPO

Figure 97.

SFDR ACROSS TEMPERATURE vs AVDD SUPPLY

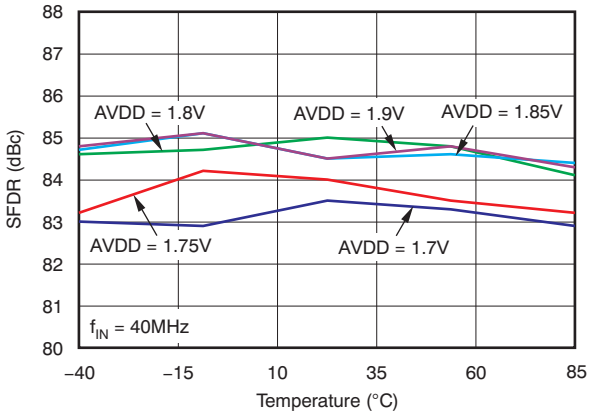


Figure 98.

SNR ACROSS TEMPERATURE vs AVDD SUPPLY

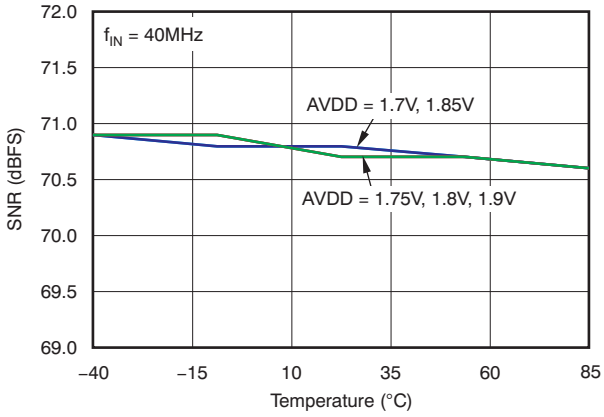


Figure 99.

PERFORMANCE ACROSS DRVDD SUPPLY VOLTAGE

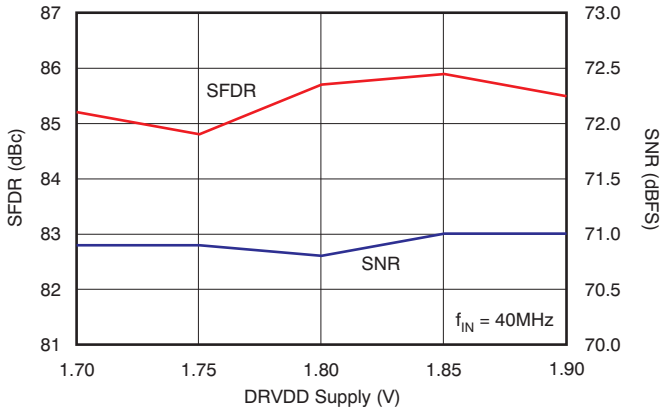


Figure 100.

PERFORMANCE ACROSS DRVDD SUPPLY VOLTAGE (CMOS)

FPO

Figure 101.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: ADS4126 (continued)

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

PERFORMANCE ACROSS INPUT CLOCK AMPLITUDE

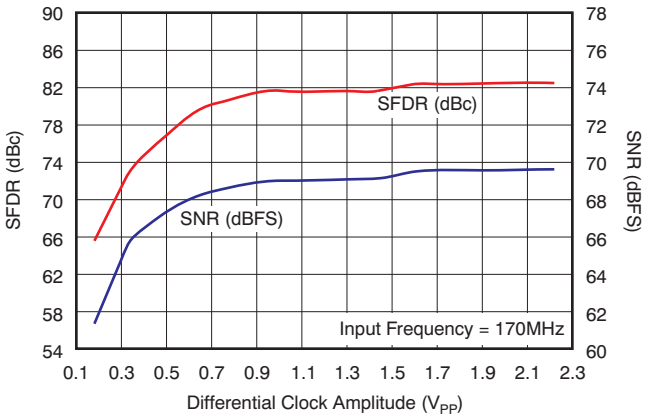


Figure 102.

PERFORMANCE ACROSS INPUT CLOCK DUTY CYCLE

Figure 103.

INTEGRAL NONLINEARITY

Figure 104.

DIFFERENTIAL NONLINEARITY

Figure 105.

OUTPUT HISTOGRAM WITH INPUTS SHORTED

Figure 106.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: COMMON

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

CMRR ACROSS FREQUENCY

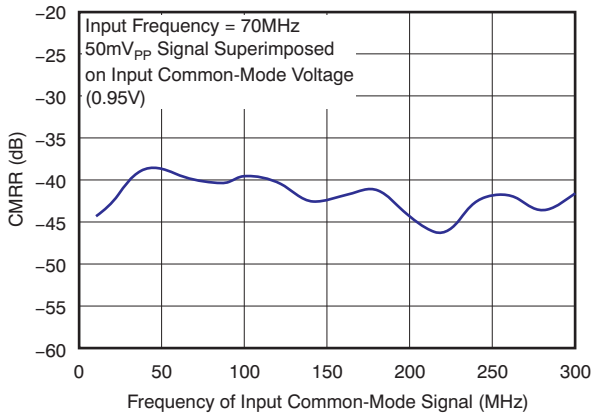


Figure 107.

SPECTRUM SHOWING EFFECT OF CM SIGNAL

Figure 108.

PSRR ACROSS FREQUENCY

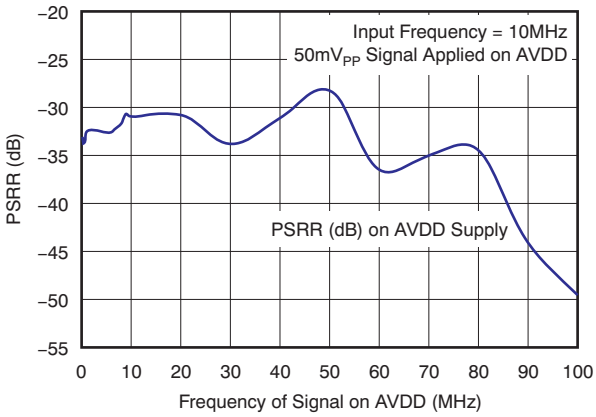


Figure 109.

SPECTRUM SHOWING EFFECT OF SIGNAL ON SUPPLY

Figure 110.

POWER ACROSS SAMPLING FREQUENCY

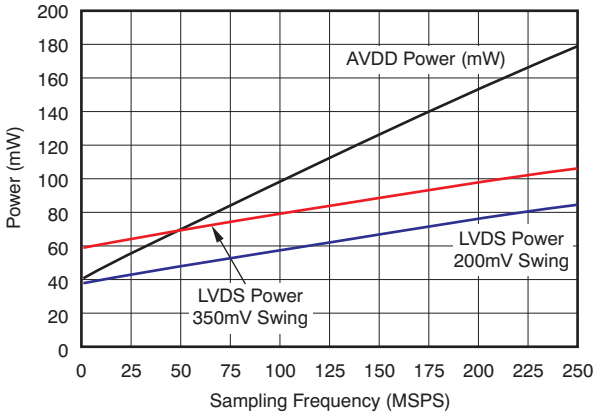


Figure 111.

DRVDD CURRENT ACROSS SAMPLING FREQUENCY

Figure 112.

PRODUCT PREVIEW

TYPICAL CHARACTERISTICS: CONTOUR

At +25°C, AVDD = 1.8V, DRVDD = 1.8V, maximum rated sampling frequency, sine wave input clock, 1.5V_{PP} differential clock amplitude, 50% clock duty cycle, –1dBFS differential analog input, internal reference mode, low-latency mode, 0dB gain, DDR LVDS output interface, and 32k-point FFT, unless otherwise noted.

SFDR ACROSS INPUT AND SAMPLING FREQUENCIES (0dB Gain)

Figure 113.

SFDR ACROSS INPUT AND SAMPLING FREQUENCIES (6dB Gain)

Figure 114.

SNR ACROSS INPUT AND SAMPLING FREQUENCIES (0dB Gain)

Figure 115.

SNR ACROSS INPUT AND SAMPLING FREQUENCIES (6dB Gain)

Figure 116.

PRODUCT PREVIEW

APPLICATION INFORMATION

THEORY OF OPERATION

The ADS414x/2x is a family of high-performance and low-power 12-bit and 14-bit ADCs with maximum sampling rates up to 250MSPS. The conversion process is initiated by a rising edge of the external input clock and the analog input signal is sampled. The sampled signal is sequentially converted by a series of small resolution stages, with the outputs combined in a digital correction logic block. At every clock edge the sample propagates through the pipeline, resulting in a data latency of **TBD** clock cycles. The output is available as 14-bit data or 12-bit data, in DDR LVDS mode or CMOS mode, and coded in either straight offset binary or binary twos complement format.

ANALOG INPUT

The analog input consists of a switched-capacitor-based differential sample-and-hold architecture. This differential topology results in very good ac performance even for high input frequencies at high sampling rates. The INP and INM pins must be externally biased around a common-mode voltage of 0.95V, available on the VCM pin. For a full-scale differential input, each input INP and INM pin must swing symmetrically between (VCM + 0.5V) and (VCM – 0.5V), resulting in a $2V_{PP}$ differential input swing. The input sampling circuit has a high 3dB bandwidth that extends up to 550MHz (measured from the input pins to the sampled voltage). Figure 117 shows an equivalent circuit for the analog input.

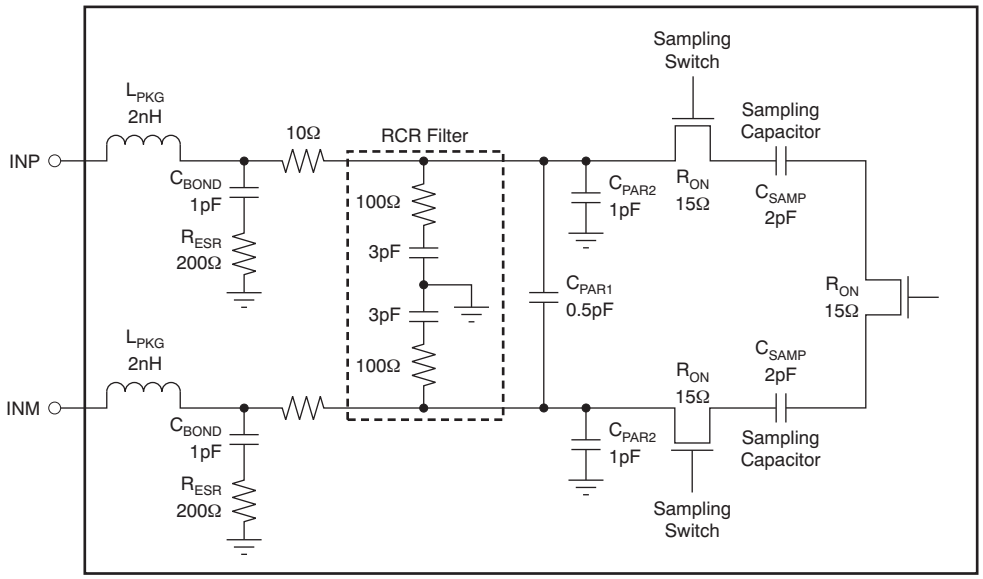


Figure 117. Analog Input Equivalent Circuit

Drive Circuit Requirements

For optimum performance, the analog inputs must be driven differentially. This technique improves the common-mode noise immunity and even-order harmonic rejection. A 5Ω to 15Ω resistor in series with each input pin is recommended to damp out ringing caused by package parasitics. It is also necessary to present low impedance (less than 50Ω) for the common-mode switching currents. This impedance can be achieved by using two resistors from each input terminated to the common-mode voltage (VCM).

Note that the device includes an internal R-C filter from each input to ground. The purpose of this filter is to absorb the glitches caused by the opening and closing of the sampling capacitors. The cutoff frequency of the R-C filter involves a trade-off. A lower cutoff frequency (larger C) absorbs glitches better, but also reduces the input bandwidth and the maximum input frequency that can be supported. On the other hand, with no internal R-C filter, high input frequency can be supported but now the sampling glitches must be supplied by the external driving circuit. The inductance of the package bond wires limits the ability of the external driving circuit to support the sampling glitches.

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In the ADS414x/2x, the R-C component values have been optimized while supporting high input bandwidth (550MHz). However, in applications where very high input frequency support is not required, filtering of the glitches can be improved further with an external R-C-R filter; see Figure 120 and Figure 121).

In addition, the drive circuit may have to be designed to provide a low insertion loss over the desired frequency range and matched impedance to the source. While designing the drive circuit, the ADC impedance must be considered. Figure 118 and Figure 119 show the impedance ($Z_{IN} = R_{IN} \parallel C_{IN}$) looking into the ADC input pins.

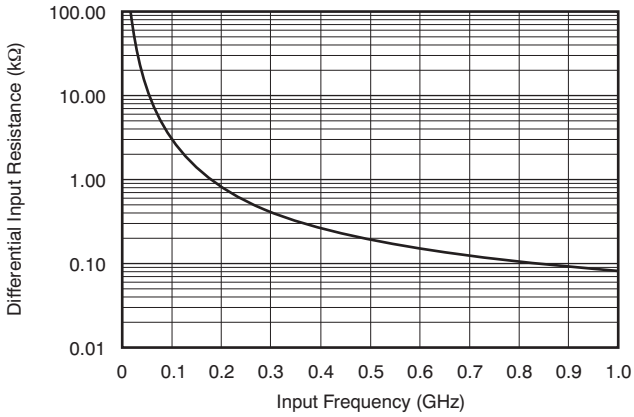

Figure 118. ADC Analog Input Resistance (R_{IN}) Across Frequency

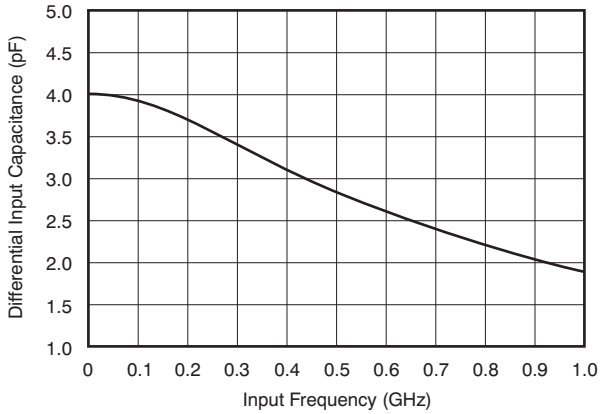

Figure 119. ADC Analog Input Capacitance (C_{IN}) Across Frequency

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Driving Circuit

Two example driving circuit configurations are shown in Figure 120 and Figure 121—one optimized for low bandwidth (tlow input frequencies) and the other one for high bandwidth to support higher input frequencies. In Figure 120, an external R-C-R filter with 3.3pF is used to help absorb sampling glitches. The R-C-R filter limits the bandwidth of the drive circuit, making it suitable for low input frequencies (up to 250MHz). Transformers such as ADT1-1WT or WBC1-1 can be used up to 250MHz.

For higher input frequencies, the R-C-R filter can be dropped. Together with the lower series resistors (5Ω to 10Ω), this drive circuit provides higher bandwidth to support frequencies up to 500MHz (as shown in Figure 121). A transmission line transformer such as ADTL2-18 can be used.

Note that both the drive circuits have been terminated by 50Ω near the ADC side. The termination is accomplished by a 25Ω resistor from each input to the 0.95V common-mode (VCM) from the device. This termination allows the analog inputs to be biased around the required common-mode voltage.

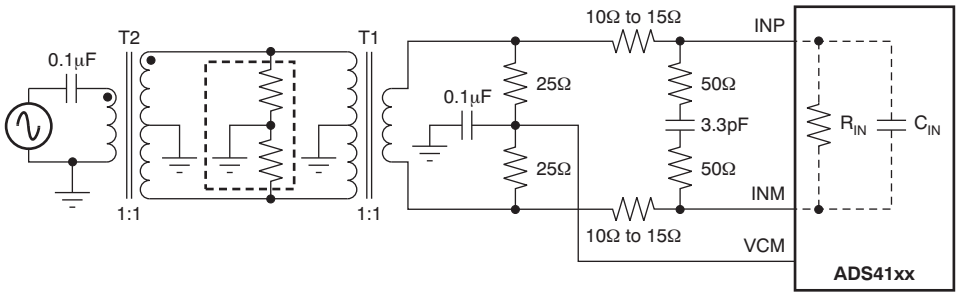

Figure 120. Drive Circuit with Low Bandwidth (for Low Input Frequencies)

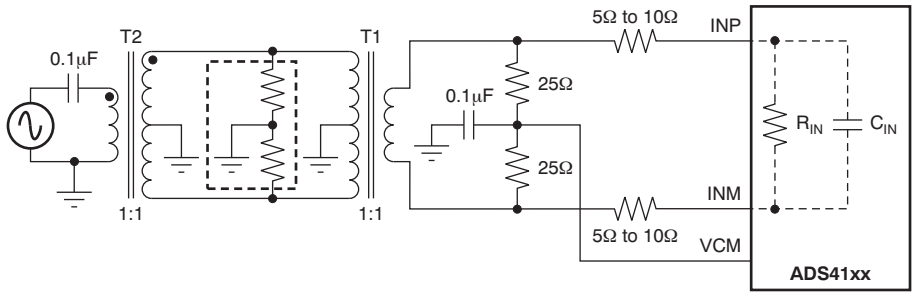

Figure 121. Drive Circuit with High Bandwidth (for High Input Frequencies)

PRODUCT PREVIEW

The mismatch in the transformer parasitic capacitance (between the windings) results in degraded even-order harmonic performance. Connecting two identical RF transformers back-to-back helps minimize this mismatch and good performance is obtained for high-frequency input signals. An additional termination resistor pair may be required between the two transformers, as shown in Figure 120 and Figure 121. The center point of this termination is connected to ground to improve the balance between the P (positive) and M (negative) sides. The values of the terminations between the transformers and on the secondary side must be chosen to obtain an effective 50Ω (for a 50Ω source impedance).

Figure 120 and Figure 121 use 1:1 transformers with a 50Ω source. As explained in the *Drive Circuit Requirements* section, this architecture helps to present a low source impedance to absorb sampling glitches. With a 1:4 transformer, the source impedance is 200Ω. The higher source impedance is unable to absorb the sampling glitches effectively and can lead to degradation in performance (compared to using 1:1 transformers).

In almost all cases, either a bandpass or low-pass filter is needed to get the desired dynamic performance, as shown in Figure 122. Such a filter presents low source impedance at the high frequencies corresponding to the sampling glitch and helps avoid the performance loss with the high source impedance.

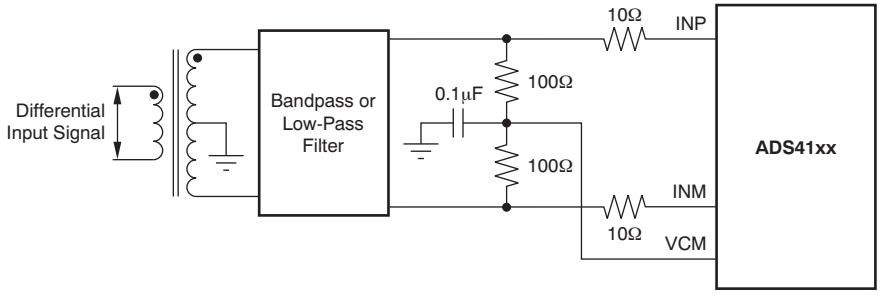

Figure 122. Drive Circuit with 1:4 Transformer

Input Common-Mode

To ensure a low-noise, common-mode reference, the VCM pin is filtered with a 0.1µF low-inductance capacitor connected to ground. The VCM pin is designed to directly drive the ADC inputs. The input stage of the ADC sinks a common-mode current in the order of **TBD**µA (per input pin, at 250MSPS). Equation 1 describes the dependency of the common-mode current and the sampling frequency.

FPO

(1)

Equation 1 helps to design the output capability and impedance of the CM driving circuit accordingly.

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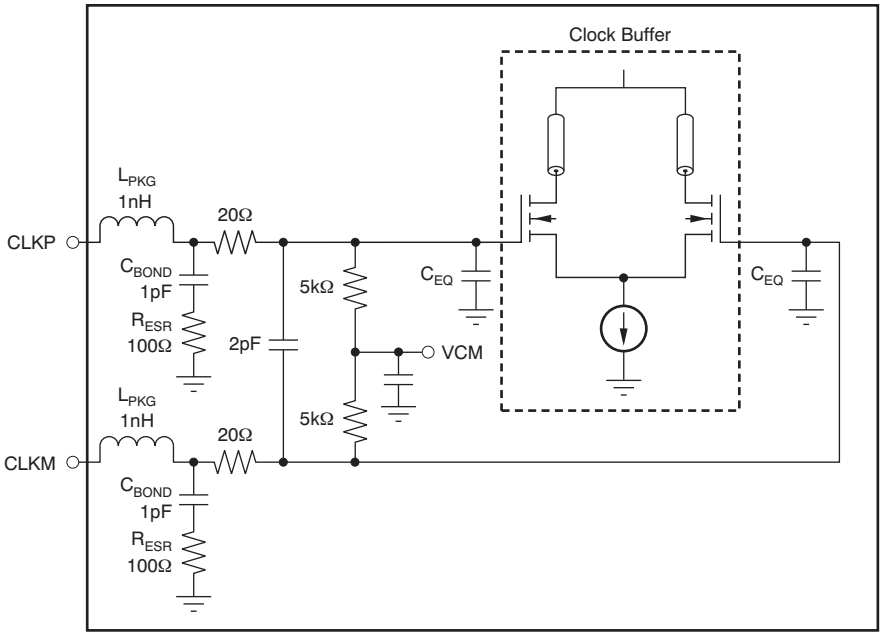
CLOCK INPUT

The ADS414x/2x clock inputs can be driven differentially (sine, LVPECL, or LVDS) or single-ended (LVCMOS), with little or no difference in performance between them. The common-mode voltage of the clock inputs is set to VCM using internal 5kΩ resistors. This setting allows the use of transformer-coupled drive circuits for sine-wave clock or ac-coupling for LVPECL and LVDS clock sources. Figure 123 shows an equivalent circuit for the input clock.



NOTE: C_{EQ} is 1pF to 3pF and is the equivalent input capacitance of the clock buffer.

Figure 123. Input Clock Equivalent Circuit

A single-ended CMOS clock can be ac-coupled to the CLKP input, with CLKM connected to ground with a 0.1µF capacitor, as shown in Figure 124. For best performance, the clock inputs must be driven differentially, reducing susceptibility to common-mode noise. For high input frequency sampling, it is recommended to use a clock source with very low jitter. Band-pass filtering of the clock source can help reduce the effects of jitter. There is no change in performance with a non-50% duty cycle clock input. Figure 125 shows a differential circuit.

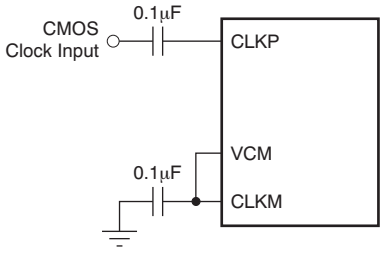


Figure 124. Single-Ended Clock Driving Circuit

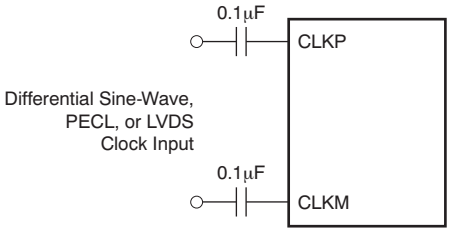


Figure 125. Differential Clock Driving Circuit

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DIGITAL FUNCTIONS AND LOW LATENCY MODE

The device has several useful digital functions such as test patterns, gain, and offset correction. All of these functions require extra clock cycles for operation and increase the overall latency and power of the device. Alternately, the device has a low-latency mode in which the raw ADC output is routed to the output data pins with a latency of **TBD** clock cycles. In this mode, the digital functions are bypassed. Figure 126 shows more details of the processing after the ADC.

The device is in low-latency mode after reset. In order to use any of the digital functions, first the low-latency mode must be disabled by setting the DIS LOW LATENCY register bit to '1'. After this, the respective register bits must be programmed as described in the following sections and in the *Serial Register Map* section.

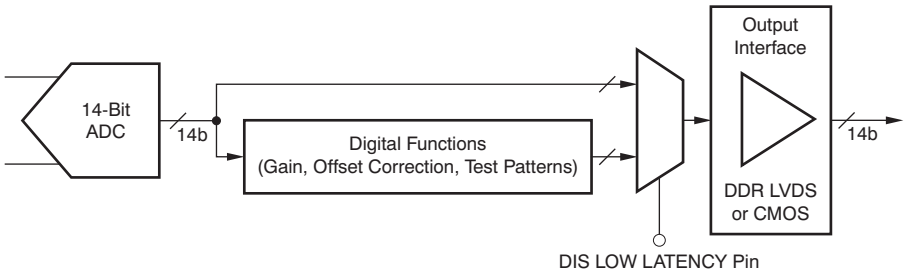

Figure 126. Digital Processing Block Diagram

FINE GAIN FOR SFDR/SNR TRADE-OFF

The ADS414x/2x include gain settings that can be used to get improved SFDR performance. The gain is programmable from 0dB to 6dB (in 0.5dB steps) using the GAIN register bits. For each gain setting, the analog input full-scale range scales proportionally, as shown in Table 8.

The SFDR improvement is achieved at the expense of SNR; for each gain setting, the SNR degrades approximately between 0.5dB and 1dB. The SNR degradation is reduced at high input frequencies. As a result, the fine gain is very useful at high input frequencies because the SFDR improvement is significant with marginal degradation in SNR. Therefore, the fine gain can be used to trade-off between SFDR and SNR.

After a reset, the device is in low-latency mode and gain function is disabled. To use fine gain:

- First, disable the low-latency mode (DIS LOW LATENCY = 1).
- This setting enables the gain and puts the device in a 0dB gain mode.
- For other gain settings, program the GAIN bits.

Table 8. Full-Scale Range Across Gains

GAIN (dB)	TYPE	FULL-SCALE (V_{PP})
0	Default after reset	2
1	Fine, programmable	1.78
2	Fine, programmable	1.59
3	Fine, programmable	1.42
4	Fine, programmable	1.26
5	Fine, programmable	1.12
6	Fine, programmable	1.00

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OFFSET CORRECTION

The ADS414x/2x has an internal offset corretion algorithm that estimates and corrects dc offset up to ±**TBD**mV. The correction can be enabled using the EN OFFSET CORR serial register bit. Once enabled, the algorithm estimates the channel offset and applies the correction every clock cycle. The time constant of the correction loop is a function of the sampling clock frequency. The time constant can be controlled using the OFFSET CORR TIME CONSTANT register bits, as described in Table 9.

Table 9. Time Constant of Offset Correction Algorithm

OFFSET CORR TIME CONSTANT	TIME CONSTANT, TC_{CLK} (Number of Clock Cycles)	TIME CONSTANT, $TC_{CLK} \times 1/f_S$ (sec)(1)
TBD	TBD	TBD
TBD	TBD	TBD

(1) Sampling frequency, f_S = 250MSPS.

After the offset is estimated, the correction can be frozen by setting FREEZE OFFSET CORR = 1. Once frozen, the last estimated value is used for the offset correction of every clock cycle. Note that offset correction is disabled by a default after reset.

After a reset, the device is in low-latency mode and offset correction is disabled. To use offset correction:

- First, disable the low-latency mode (DIS LOW LATENCY = 1).
- Then set EN OFFSET CORR to '1' and program the required time constant.

Figure 127 shows the time response of the offset correction algorithm after it is enabled.

Figure 127. Time Response of Offset Correction

POWER DOWN

The ADS414x/2x has three power-down modes: power-down global, standby, and output buffer disable.

Power-Down Global

In this mode, the entire chip (including the ADC, internal reference, and the output buffers) are powered down, resulting in reduced total power dissipation of about **TBD**mW. The output buffers are in a high-impedance state. The wake-up time from the global power-down to data becoming valid in normal mode is typically **TBD**µs. This can be controlled using the PDN GLOBAL register bit.

Standby

In this mode, only the ADC is powered down and the internal references are active, resulting in a fast wake-up time of **TBD**ns. The total power dissipation in standby mode is approximately **TBD**mW. This can be controlled using the STBY register bit.

Output Buffer Disable

The output buffers can be disabled and put in a high-impedance state; wakeup time from this mode is fast, approximately **TBD**ns. This can be controlled using the PDN OBUF register bit or using the OE pin.

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Input Clock Stop

In addition, the converter enters a low-power mode when the input clock frequency falls below 1MSPS. The power dissipation is about **TBD**mW.

POWER-SUPPLY SEQUENCE

During power-up, the AVDD and DRVDD supplies can come up in any sequence. The two supplies are separated in the device. Externally, they can be driven from separate supplies or from a single supply.

DIGITAL OUTPUT INFORMATION

The ADS414x/2x provide either 14-bit data or 12-bit data, respectively, and an output clock synchronized with the data.

Output Interface

Two output interface options are available: double data rate (DDR) LVDS and parallel CMOS. They can be selected using the LVDS CMOS serial interface register bit or using the DFS pin.

DDR LVDS Outputs

In this mode, the data bits and clock are output using low voltage differential signal (LVDS) levels. Two data bits are multiplexed and output on each LVDS differential pair, as shown in Figure 128 and Figure 129.

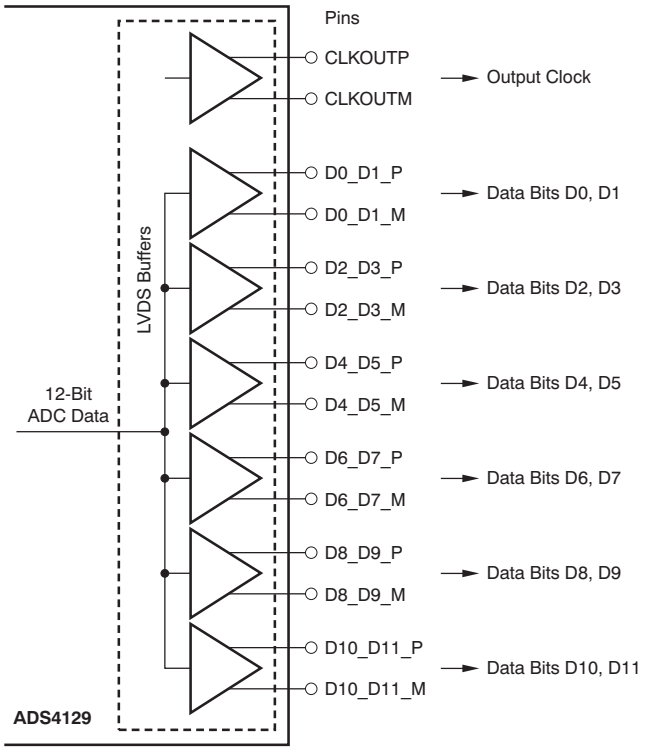

Figure 128. ADS412x LVDS Data Outputs

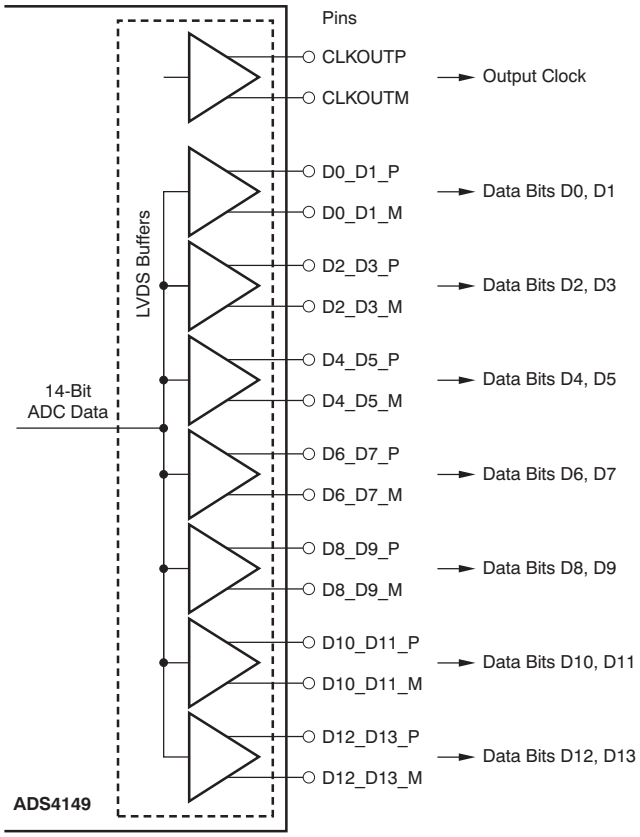

Figure 129. ADS414x LVDS Data Outputs

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Even data bits (D0, D2, D4, etc.) are output at the falling edge of CLKOUTP and the odd data bits (D1, D3, D5, etc.) are output at the rising edge of CLKOUTP. Both the rising and falling edges of CLKOUTP must be used to capture all 14 data bits, as shown in Figure 130.

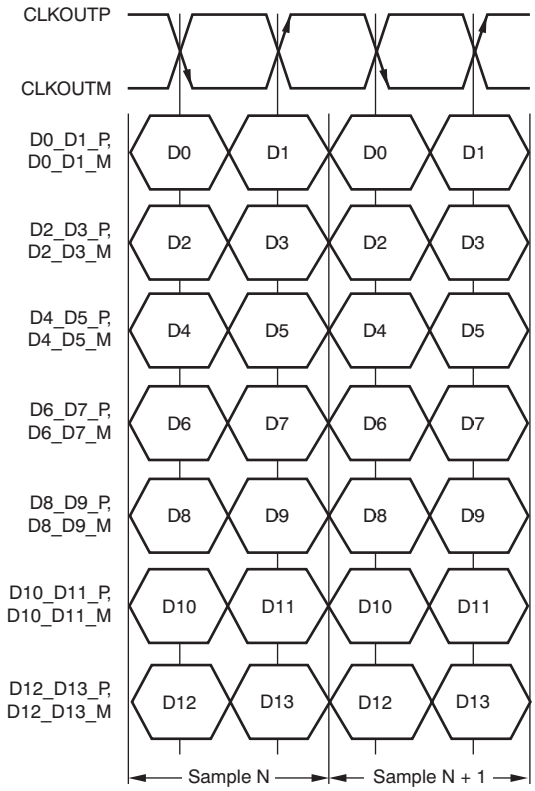


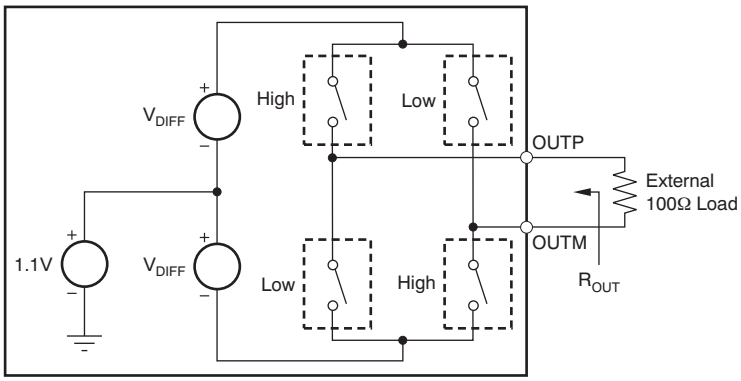
Figure 130. DDR LVDS Interface

LVDS Output Data and Clock Buffers

The equivalent circuit of each LVDS output buffer is shown in Figure 131. After reset, the buffer presents an output impedance of 100Ω to match with the external 100Ω termination.

Additionally, a mode exists to double the strength of the LVDS buffer to support 50Ω differential termination. This mode can be used when the output LVDS signal is routed to two separate receiver chips, each using a 100Ω termination. The mode can be enabled using the LVDS DATA STRENGTH and LVDS CLKOUT STRENGTH register bits for data and output clock buffers, respectively.

The buffer output impedance behaves in the same way as a source-side series termination. By absorbing reflections from the receiver end, it helps to improve signal integrity.



NOTE: Use the default buffer strength to match 100Ω external termination (R_{OUT} = 100Ω). To match with a 50Ω external termination, set the LVDS STRENGTH bit (R_{OUT} = 50Ω).

When the high switches are closed, OUTP = 1.275V and OUTM = 0.925V. When the low switches are closed, OUTP = 0.925V and OUTM = 1.275V.

Figure 131. LVDS Buffer Equivalent Circuit

Parallel CMOS Interface

In CMOS mode, each data bit is output on a separate pin as CMOS voltage level, for every clock cycle. The rising edge of the output clock CLKOUT can be used to latch data in the receiver (for sampling frequencies up to **TBD**MSPS). Figure 132 depicts the CMOS output interface.

The setup and hold timing of the output data with respect to CLKOUT are specified, up to **TBD**MSPS. It is recommended to minimize the load capacitance seen by data and clock output pins by using short traces to the receiver. Also, match the output data and clock traces to minimize the skew between them.

For sampling frequencies above **TBD**MSPS, it is recommended to use an external clock to capture data. The delay from input clock to output data and the data valid times are specified for the higher sampling frequencies. These timings can be used to delay the input clock appropriately and use it to capture the data.

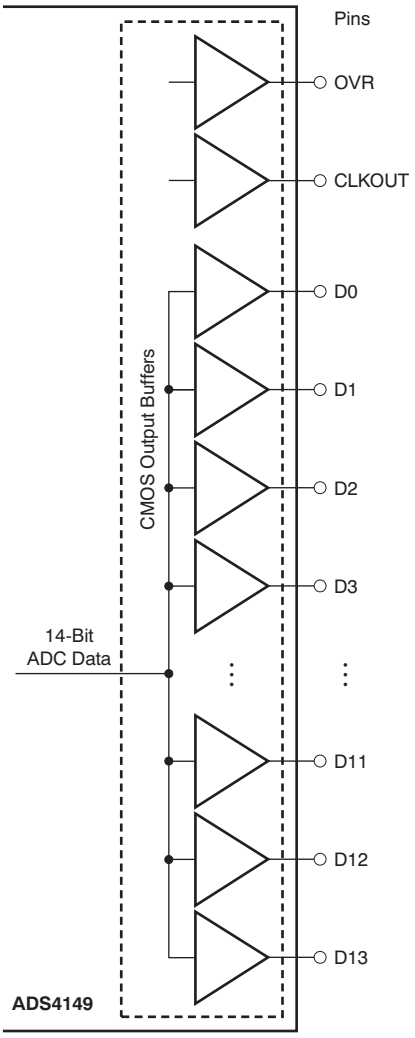


Figure 132. CMOS Output Interface

Output Buffer Strength Programmability

Switching noise (caused by CMOS output data transitions) can couple into the analog inputs during the instant of sampling and degrade the SNR. The coupling and SNR degradation increases as the output buffer drive is made stronger. To minimize this effect, the CMOS output buffers are designed with controlled drive strength to obtain the best SNR. The default drive strength also ensures a wide data stable window for load capacitances up to 5pF.

CMOS Interface Power Dissipation

With CMOS outputs, the DRVDD current scales with the sampling frequency and the load capacitance on every output pin. The maximum DRVDD current occurs when each output bit toggles between '0' and '1' every clock cycle. In actual applications, this condition is unlikely to occur. The actual DRVDD current would be determined by the average number of output bits switching, which is a function of the sampling frequency and the nature of the analog input signal.

Digital Current as a Result of CMOS Output Switching = $C_L \times DRVDD \times (N \times f_{AVG})$

where:

C_L = load capacitance,

$N \times F_{AVG}$ = average number of output bits switching.

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Figure TBD shows the current across sampling frequencies at 2 MHz analog input frequency.

Input Over-Voltage Indication (OVR Pin)

The device has an OVR pin that provides information about analog input overload. At any clock cycle, if the sampled input voltage exceeds the positive or negative full-scale range, the OVR pin goes high. The OVR remains high as long as the overload condition persists. The OVR pin is a CMOS output buffer (running off DRVDD supply), independent of the type of output data interface (DDR LVDS or CMOS).

For a positive overload, the D[13:0] output data bits are 0x3FFF in offset binary output format and 0x1FFF in twos complement output format. For a negative input overload, the output code is 0x0000 in offset binary output format and 0x2000 in twos complement output format.

Output Data Format

Two output data formats are supported: twos complement and offset binary. They can be selected using the DATA FORMAT serial interface register bit or controlling the DFS pin in parallel configuration mode. In the event of an input voltage overdrive, the digital outputs go to the appropriate full-scale level.

BOARD DESIGN CONSIDERATIONS

Grounding

A single ground plane is sufficient to give good performance, provided the analog, digital, and clock sections of the board are cleanly partitioned. See the *ADS414x, ADS412x EVM User Guide* (SLWU067) for details on layout and grounding.

Supply Decoupling

Because the ADS414x/2x already include internal decoupling, minimal external decoupling can be used without loss in performance. Note that decoupling capacitors can help filter external power-supply noise, so the optimum number of capacitors depends on the actual application. The decoupling capacitors should be placed very close to the converter supply pins.

Exposed Pad

In addition to providing a path for heat dissipation, the PowerPAD is also electrically internally connected to the digital ground. Therefore, it is necessary to solder the exposed pad to the ground plane for best thermal and electrical performance. For detailed information, see application notes *QFN Layout Guidelines* (SLOA122) and *QFN/SON PCB Attachment* (SLUA271), both available for download at the TI web site (www.ti.com).

DEFINITION OF SPECIFICATIONS

Analog Bandwidth – The analog input frequency at which the power of the fundamental is reduced by 3 dB with respect to the low-frequency value.

Aperture Delay – The delay in time between the rising edge of the input sampling clock and the actual time at which the sampling occurs. This delay is different across channels. The maximum variation is specified as aperture delay variation (channel-to-channel).

Aperture Uncertainty (Jitter) – The sample-to-sample variation in aperture delay.

Clock Pulse Width/Duty Cycle – The duty cycle of a clock signal is the ratio of the time the clock signal remains at a logic high (clock pulse width) to the period of the clock signal. Duty cycle is typically expressed as a percentage. A perfect differential sine-wave clock results in a 50% duty cycle.

Maximum Conversion Rate – The maximum sampling rate at which specified operation is given. All parametric testing is performed at this sampling rate unless otherwise noted.

Minimum Conversion Rate – The minimum sampling rate at which the ADC functions.

Differential Nonlinearity (DNL) – An ideal ADC exhibits code transitions at analog input values spaced exactly 1 LSB apart. The DNL is the deviation of any single step from this ideal value, measured in units of LSBs.

Integral Nonlinearity (INL) – The INL is the deviation of the ADC transfer function from a best fit line determined by a least squares curve fit of that transfer function, measured in units of LSBs.

Gain Error – Gain error is the deviation of the ADC actual input full-scale range from its ideal value. The gain error is given as a percentage of the ideal input full-scale range. Gain error has two components: error as a result of reference inaccuracy and error as a result of the channel. Both errors are specified independently as E_{GREF} and E_{GCHAN}.

To a first-order approximation, the total gain error is $E_{TOTAL} \sim E_{GREF} + E_{GCHAN}$.

For example, if $E_{TOTAL} = \pm 0.5\%$, the full-scale input varies from $(1 - 0.5/100) \times FS_{ideal}$ to $(1 + 0.5/100) \times FS_{ideal}$.

Offset Error – The offset error is the difference, given in number of LSBs, between the ADC actual average idle channel output code and the ideal average idle channel output code. This quantity is often mapped into millivolts.

Temperature Drift – The temperature drift coefficient (with respect to gain error and offset error) specifies the change per degree Celsius of the parameter from T_{MIN} to T_{MAX}. It is calculated by dividing the maximum deviation of the parameter across the T_{MIN} to T_{MAX} range by the difference $T_{MAX} – T_{MIN}$.

Signal-to-Noise Ratio – SNR is the ratio of the power of the fundamental (P_S) to the noise floor power (P_N), excluding the power at dc and the first nine harmonics.

$$SNR = 10Log^{10} \frac{P_S}{P_N} \quad (3)$$

SNR is either given in units of dBc (dB to carrier) when the absolute power of the fundamental is used as the reference, or dBFS (dB to full-scale) when the power of the fundamental is extrapolated to the converter full-scale range.

Signal-to-Noise and Distortion (SINAD) – SINAD is the ratio of the power of the fundamental (P_S) to the power of all the other spectral components including noise (P_N) and distortion (P_D), but excluding dc.

$$SINAD = 10Log^{10} \frac{P_S}{P_N + P_D} \quad (4)$$

SINAD is either given in units of dBc (dB to carrier) when the absolute power of the fundamental is used as the reference, or dBFS (dB to full-scale) when the power of the fundamental is extrapolated to the converter full-scale range.

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Effective Number of Bits (ENOB) – ENOB is a measure of the converter performance as compared to the theoretical limit based on quantization noise.

$$\text{ENOB} = \frac{\text{SINAD} - 1.76}{6.02} \tag{5}$$

Total Harmonic Distortion (THD) – THD is the ratio of the power of the fundamental (P_S) to the power of the first nine harmonics (P_D).

$$\text{THD} = 10\text{Log}^{10} \frac{P_S}{P_N} \tag{6}$$

THD is typically given in units of dBc (dB to carrier).

Spurious-Free Dynamic Range (SFDR) – The ratio of the power of the fundamental to the highest other spectral component (either spur or harmonic). SFDR is typically given in units of dBc (dB to carrier).

Two-Tone Intermodulation Distortion – IMD3 is the ratio of the power of the fundamental (at frequencies f_1 and f_2) to the power of the worst spectral component at either frequency $2f_1 – f_2$ or $2f_2 – f_1$. IMD3 is either given in units of dBc (dB to carrier) when the absolute power of the fundamental is used as the reference, or dBFS (dB to full-scale) when the power of the fundamental is extrapolated to the converter full-scale range.

DC Power-Supply Rejection Ratio (DC PSRR) – DC PSSR is the ratio of the change in offset error to a change in analog supply voltage. The dc PSRR is typically given in units of mV/V.

AC Power-Supply Rejection Ratio (AC PSRR) – AC PSRR is the measure of rejection of variations in the supply voltage by the ADC. If ΔV_{SUP} is the change in supply voltage and ΔV_{OUT} is the resultant change of the ADC output code (referred to the input), then:

$$\text{PSRR} = 20\text{Log}^{10} \frac{\Delta V_{OUT}}{\Delta V_{SUP}} \text{ (Expressed in dBc)} \tag{7}$$

Voltage Overload Recovery – The number of clock cycles taken to recover to less than 1% error after an overload on the analog inputs. This is tested by separately applying a sine wave signal with 6dB positive and negative overload. The deviation of the first few samples after the overload (from the expected values) is noted.

Common-Mode Rejection Ratio (CMRR) – CMRR is the measure of rejection of variation in the analog input common-mode by the ADC. If ΔV_{CM_IN} is the change in the common-mode voltage of the input pins and ΔV_{OUT} is the resulting change of the ADC output code (referred to the input), then:

$$\text{CMRR} = 20\text{Log}^{10} \frac{\Delta V_{OUT}}{\Delta V_{CM}} \text{ (Expressed in dBc)} \tag{8}$$

Crosstalk (only for multi-channel ADCs) – This is a measure of the internal coupling of a signal from an adjacent channel into the channel of interest. It is specified separately for coupling from the immediate neighboring channel (near-channel) and for coupling from channel across the package (far-channel). It is usually measured by applying a full-scale signal in the adjacent channel. Crosstalk is the ratio of the power of the coupling signal (as measured at the output of the channel of interest) to the power of the signal applied at the adjacent channel input. It is typically expressed in dBc.

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PACKAGING INFORMATION

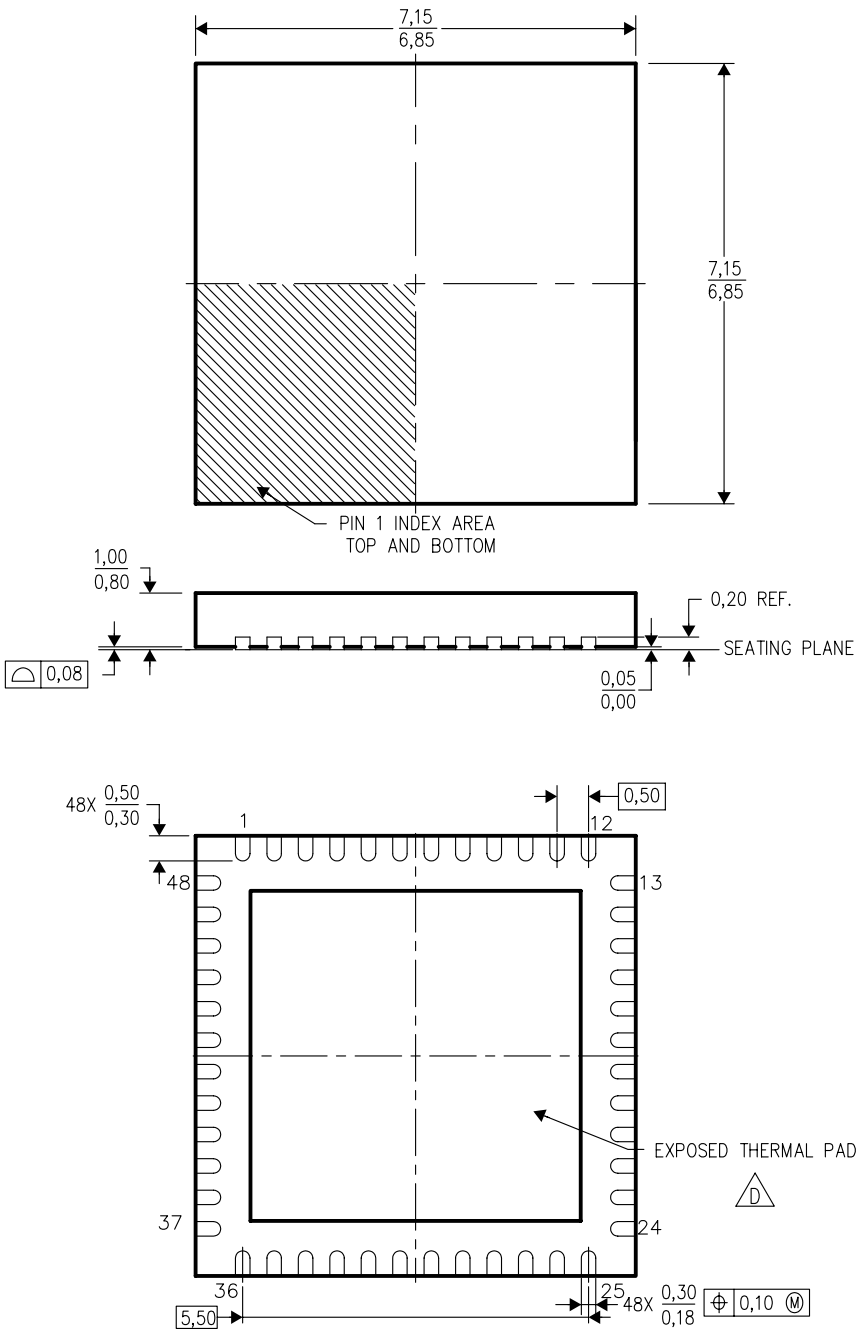
Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)
ADS4126IRGZR	PREVIEW	QFN	RGZ	48		TBD	Call TI	Call TI
ADS4126IRGZT	PREVIEW	QFN	RGZ	48		TBD	Call TI	Call TI
ADS4129IRGZR	PREVIEW	QFN	RGZ	48	2500	TBD	Call TI	Call TI
ADS4129IRGZT	PREVIEW	QFN	RGZ	48	250	TBD	Call TI	Call TI
ADS4146IRGZR	PREVIEW	QFN	RGZ	48		TBD	Call TI	Call TI
ADS4146IRGZT	PREVIEW	QFN	RGZ	48		TBD	Call TI	Call TI
ADS4149IRGZR	PREVIEW	QFN	RGZ	48	2500	TBD	Call TI	Call TI
ADS4149IRGZT	PREVIEW	QFN	RGZ	48	250	TBD	Call TI	Call TI
PADS4149IRGZT	PREVIEW	QFN	RGZ	48	250	TBD	Call TI	Call TI

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

RGZ (S–PQFP–N48) PLASTIC QUAD FLATPACK



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Quad Flatpack, No–leads (QFN) package configuration.
D. The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.
E. Falls within JEDEC MO–220.

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